TS419
TS421

360mW MONO AMPLIFIER WITH STANDBY MODE

- **OPERATING FROM Vcc=2V to 5.5V**
- **STANDBY MODE** ACTIVE HIGH (TS419) or LOW (TS421)
- OUTPUT POWER into 16Ω: 367mW @ 5V with 10% THD+N max or 295mW @5V and 110mW @3.3V with 1% THD+N max.
- **LOW CURRENT CONSUMPTION:** 2.5mA max
- High Signal-to-Noise ratio: 95dB(A) at 5V
- PSRR: 56dB typ. at 1kHz, 46dB at 217Hz
- **SHORT CIRCUIT LIMITATION**
- ON/OFF click reduction circuitry
- Available in SO8, **MiniSO8 & DFN 3x3**

DESCRIPTION

The TS419/TS421 is a monaural audio power amplifier driving in BTL mode a 16 or 32Ω earpiece or receiver speaker. The main advantage of this configuration is to get rid of bulky ouput capacitors.
Capable of descending to low voltages, it delivers up to 220mW per channel (into 16Ω loads) of continuous average power with 0.2% THD+N in the audio bandwidth from a 5V power supply.
An externally controlled standby mode reduces the supply current to 10nA (typ.). The TS419/TS421 can be configured by external gain-setting resistors or used in a fixed gain version.

APPLICATIONS

- 16/32 ohms earpiece or receiver speaker driver
- Mobile and cordless phones (analog / digital)
- PDAs & computers
- Portable appliances

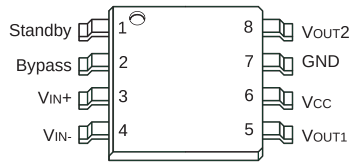
ORDER CODE

Part Number	Temp. Range: I	Package			Gain	Marking
		D	S	Q		
TS419	-40, +85°C	•			external	TS419I
TS421		•			external	TS421I
TS419			•	•	external	K19A
TS419-2			tba	tba	x2/6dB	K19B
TS419-4			tba	tba	x4/12dB	K19C
TS419-8			tba	tba	x8/18dB	K19D
TS421			•	•	external	K21A
TS421-2			tba	tba	x2/6dB	K21B
TS421-4			tba	tba	x4/12dB	K21C
TS421-8			tba	tba	x8/18dB	K21D

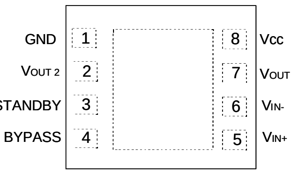
MiniSO & DFN only available in Tape & Reel with T suffix.
SO is available in Tube (D) and in Tape & Reel (DT)

PIN CONNECTIONS (top view)

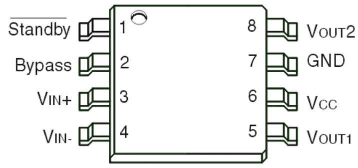
TS419IDT: SO8
TS419IST, TS419-xIST: MiniSO8



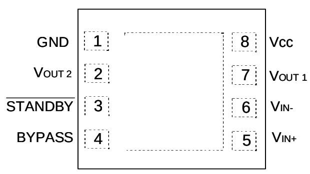
TS419IQT, TS419-xIQT: DFN8



TS421IDT: SO8
TS421IST, TS421-xIST: MiniSO8



TS421IQT, TS421-xIQT: DFN8



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage [1]	6	V
V_i	Input Voltage	-0.3V to V_{CC} +0.3V	V
T_{stg}	Storage Temperature	-65 to +150	°C
T_j	Maximum Junction Temperature	150	°C
R_{thja}	Thermal Resistance Junction to Ambient SO8 MiniSO8 DFN8	 175 215 70	°C/W
Pd	Power Dissipation [2] SO8 MiniSO8 DFN8	 0.71 0.58 1.79	W
ESD	Human Body Model (pin to pin): TS419[3], TS421	1.5	kV
ESD	Machine Model - 220pF - 240pF (pin to pin)	100	V
Latch-up	Latch-up Immunity (All pins)	200	mA
	Lead Temperature (soldering, 10sec)	250	°C
	Output Short-Circuit to Vcc or GND	continous [4]	

1. All voltage values are measured with respect to the ground pin.
2. Pd has been calculated with Tamb = 25°C, Tjunction = 150°C.
3. TS419 stands 1.5KV on all pins except standby pin which stands 1KV.
4. Attention must be paid to continous power dissipation (V_{DD} x 300mA). Exposure of the IC to a short circuit for an extended time period is dramatically reducing product life expectancy.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2 to 5.5	V
R_L	Load Resistor	≥ 16	Ω
T_{oper}	Operating Free Air Temperature Range	-40 to + 85	°C
C_L	Load Capacitor R_L = 16 to 100Ω R_L > 100Ω	 400 100	pF
V_{ICM}	Common Mode Input Voltage Range	GND to V_{CC}-1V	V
V_{STB}	Standby Voltage Input TS421 ACTIVE / TS419 in STANDBY TS421 in STANDBY / TS419 ACTIVE	 $1.5 \leq V_{STB} \leq V_{CC}$ $GND \leq V_{STB} \leq 0.4$ [1]	V
R_{THJA}	Thermal Resistance Junction to Ambient SO8 MiniSO8 DFN8 [2]	 150 190 41	°C/W
T_{wu}	Wake-up time from standby to active mode (Cb = 1µF) [3]	≥ 0.12	s

1. The minimum current consumption ($I_{STANDBY}$) is guaranteed at V_{CC} (TS419) or GND (TS421) for the whole temperature range.
2. When mounted on a 4-layer PCB
3. For more details on T_{WU}, please refer to application note section on Wake-up time page 28.

FIXED GAIN VERSION SPECIFIC ELECTRICAL CHARACTERISTICS

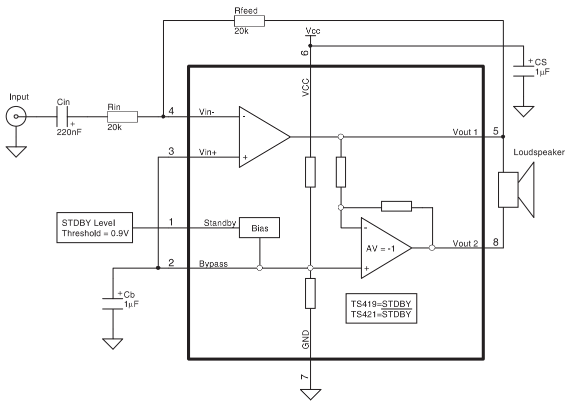
V_{CC} from **+5V to +2V**, GND = **0V**, T_{amb} = 25°C (unless otherwise specified)

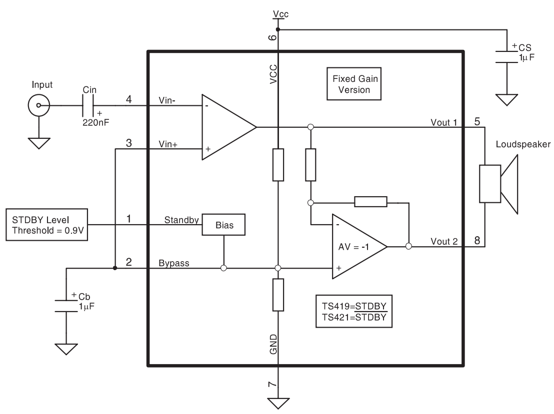
Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{IN}	Input Resistance		20		kΩ
G	Gain value for Gain TS419/TS421-2 Gain value for Gain TS419/TS421-4 Gain value for Gain TS419/TS421-8		6dB 12dB 18dB		dB

APPLICATION COMPONENTS INFORMATION

Components	Functional Description
R_{IN}	Inverting input resistor which sets the closed loop gain in conjunction with R_{FEED}. This resistor also forms a high pass filter with C_{IN} (fcl = 1 / (2 x Pi x R_{IN} x C_{IN})). **Not needed in fixed gain versions.**
C_{IN}	Input coupling capacitor which blocks the DC voltage at the amplifier's input terminal
R_{FEED}	Feedback resistor which sets the closed loop gain in conjunction with R_{IN}. A_V= Closed Loop Gain= 2xR_{FEED}/R_{IN}. **Not needed in fixed gain versions.**
C_S	Supply Bypass capacitor which provides power supply filtering.
C_B	Bypass capacitor which provides half supply filtering.

TYPICAL APPLICATION SCHEMATICS:





ELECTRICAL CHARACTERISTICS

V_{CC} = **+5V**, GND = **0V**, T_{amb} = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit
I_{CC}	Supply Current No input signal, no load		1.8	2.5	mA
$I_{STANDBY}$	Standby Current No input signal, $V_{STANDBY}$=GND for TS421 No input signal, $V_{STANDBY}$=Vcc for TS419		10	1000	nA
Voo	Output Offset Voltage No input signal, RL = 16 or 32Ω, Rfeed=20kΩ		5	25	mV
P_O	Output Power THD+N = 0.1% Max, F = 1kHz, R_L = 32Ω THD+N = 1% Max, F = 1kHz, R_L = 32Ω THD+N = 10% Max, F = 1kHz, R_L = 32Ω THD+N = 0.1% Max, F = 1kHz, R_L = 16Ω THD+N = 1% Max, F = 1kHz, R_L = 16Ω THD+N = 10% Max, F = 1kHz, R_L = 16Ω	166 240	190 207 258 270 295 367		mW
THD + N	Total Harmonic Distortion + Noise (A_V=2) R_L = 32Ω, P_{out} = 150mW, 20Hz ≤ F ≤ 20kHz R_L = 16Ω, P_{out} = 220mW, 20Hz ≤ F ≤ 20kHz		0.15 0.2		%
PSRR	Power Supply Rejection Ratio (A_V=2) [1] F = 1kHz, Vripple = 200mVpp, input grounded, Cb=1µF	50	56		dB
SNR	Signal-to-Noise Ratio (Filter Type A, A_V=2) [1] (R_L = 32Ω, THD +N < 0.5%, 20Hz ≤ F ≤ 20kHz)	85	98		dB
Φ_M	Phase Margin at Unity Gain R_L = 16Ω, C_L = 400pF		58		Degrees
GM	Gain Margin R_L = 16Ω, C_L = 400pF		18		dB
GBP	Gain Bandwidth Product R_L = 16Ω		1.1		MHz
SR	Slew Rate R_L = 16Ω		0.4		V/µS

1. Guaranteed by design and evaluation.

ELECTRICAL CHARACTERISTICS

V_{CC} = **+3.3V**, GND = **0V**, T_{amb} = 25°C (unless otherwise specified) [1)]

Symbol	Parameter	Min.	Typ.	Max.	Unit
I_{CC}	Supply Current No input signal, no load		1.8	2.5	mA
$I_{STANDBY}$	Standby Current No input signal, $V_{STANDBY}$=GND for TS421 No input signal, $V_{STANDBY}$=Vcc for TS419		10	1000	nA
Voo	Output Offset Voltage No input signal, RL = 16 or 32Ω, Rfeed=20kΩ		5	25	mV
P_O	Output Power THD+N = 0.1% Max, F = 1kHz, R_L = 32Ω THD+N = 1% Max, F = 1kHz, R_L = 32Ω THD+N = 10% Max, F = 1kHz, R_L = 32Ω THD+N = 0.1% Max, F = 1kHz, R_L = 16Ω THD+N = 1% Max, F = 1kHz, R_L = 16Ω THD+N = 10% Max, F = 1kHz, R_L = 16Ω	65 91	75 81 102 104 113 143		mW
THD + N	Total Harmonic Distortion + Noise (A_V=2) R_L = 32Ω, P_{out} = 50mW, 20Hz ≤ F ≤ 20kHz R_L = 16Ω, P_{out} = 70mW, 20Hz ≤ F ≤ 20kHz		0.15 0.2		%
PSRR	Power Supply Rejection Ratio inputs grounded, F = 1kHz, Vripple = 200mVpp, Cb=1µF	50	56		dB
SNR	Signal-to-Noise Ratio (Weighted A, A_V=2) (R_L = 32Ω, THD +N < 0.5%, 20Hz ≤ F ≤ 20kHz)	82	94		dB
Φ_M	Phase Margin at Unity Gain R_L = 16Ω, C_L = 400pF		58		Degrees
GM	Gain Margin R_L = 16Ω, C_L = 400pF		18		dB
GBP	Gain Bandwidth Product R_L = 16Ω		1.1		MHz
SR	Slew Rate R_L = 16Ω		0.4		V/µS

1. All electrical values are guaranted with correlation measurements at 2V and 5V

ELECTRICAL CHARACTERISTICS

V_{CC} = **+2.5V**, GND = **0V**, T_{amb} = 25°C (unless otherwise specified)[1)]

Symbol	Parameter	Min.	Typ.	Max.	Unit
I_{CC}	Supply Current No input signal, no load		1.7	2.5	mA
$I_{STANDBY}$	Standby Current No input signal, $V_{STANDBY}$=GND for TS421 No input signal, $V_{STANDBY}$=Vcc for TS419		10	1000	nA
Voo	Output Offset Voltage No input signal, RL = 16 or 32Ω, Rfeed=20kΩ		5	25	mV
P_O	Output Power THD+N = 0.1% Max, F = 1kHz, R_L = 32Ω THD+N = 1% Max, F = 1kHz, R_L = 32Ω THD+N = 10% Max, F = 1kHz, R_L = 32Ω THD+N = 0.1% Max, F = 1kHz, R_L = 16Ω THD+N = 1% Max, F = 1kHz, R_L = 16Ω THD+N = 10% Max, F = 1kHz, R_L = 16Ω	32 44	37 41 52 50 55 70		mW
THD + N	Total Harmonic Distortion + Noise (A_v=2) R_L = 32Ω, P_{out} = 30mW, 20Hz ≤ F ≤ 20kHz R_L = 16Ω, P_{out} = 40mW, 20Hz ≤ F ≤ 20kHz		0.15 0.2		%
PSRR	Power Supply Rejection Ratio (A_v=2) inputs grounded, F = 1kHz, Vripple = 200mVpp, Cb=1µF	50	56		dB
SNR	Signal-to-Noise Ratio (Weighted A, A_v=2) (R_L = 32Ω, THD +N < 0.5%, 20Hz ≤ F ≤ 20kHz)	80	91		dB
Φ_M	Phase Margin at Unity Gain R_L = 16Ω, C_L = 400pF		58		Degrees
GM	Gain Margin R_L = 16Ω, C_L = 400pF		18		dB
GBP	Gain Bandwidth Product R_L = 16Ω		1.1		MHz
SR	Slew Rate R_L = 16Ω		0.4		V/µS

1. All electrical values are guaranted with correlation measurements at 2V and 5V

ELECTRICAL CHARACTERISTICS

V_{CC} = **+2V**, GND = **0V**, T_{amb} = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit
I_{CC}	Supply Current No input signal, no load		1.7	2.5	mA
$I_{STANDBY}$	Standby Current No input signal, $V_{STANDBY}$=GND for TS421 No input signal, $V_{STANDBY}$=Vcc for TS419		10	1000	nA
Voo	Output Offset Voltage No input signal, RL = 16 or 32Ω, Rfeed=20kΩ		5	25	mV
P_O	Output Power THD+N = 0.1% Max, F = 1kHz, R_L = 32Ω THD+N = 1% Max, F = 1kHz, R_L = 32Ω THD+N = 10% Max, F = 1kHz, R_L = 32Ω THD+N = 0.1% Max, F = 1kHz, R_L = 16Ω THD+N = 1% Max, F = 1kHz, R_L = 16Ω THD+N = 10% Max, F = 1kHz, R_L = 16Ω	19 24	20 23 30 26 30 40		mW
THD + N	Total Harmonic Distortion + Noise (A_v=2) R_L = 32Ω, P_{out} = 13mW, 20Hz ≤ F ≤ 20kHz R_L = 16Ω, P_{out} = 20mW, 20Hz ≤ F ≤ 20kHz		0.1 0.15		%
PSRR	Power Supply Rejection Ratio (A_v=2) 1) inputs grounded, F = 1kHz, Vripple = 200mVpp, Cb=1µF	49	54		dB
SNR	Signal-to-Noise Ratio (Weighted A, A_v=2) 1) (R_L = 32Ω, THD +N < 0.5%, 20Hz ≤ F ≤ 20kHz)	80	89		dB
Φ_M	Phase Margin at Unity Gain R_L = 16Ω, C_L = 400pF		58		Degrees
GM	Gain Margin R_L = 16Ω, C_L = 400pF		20		dB
GBP	Gain Bandwidth Product R_L = 16Ω		1.1		MHz
SR	Slew Rate R_L = 16Ω		0.4		V/µS

1. Guaranteed by design and evaluation.

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Signal to Noise Ratio vs Power Supply Voltage	89 to 90	25
Noise Floor	91 to 92	25
PSRR vs Frequency	93 to 97	25 to 26

Note : All measurements made with Rin=20kΩ, Cb=1µF, and Cin=10µF unless otherwise specified.

Fig. 1: Open Loop Gain and Phase vs Frequency

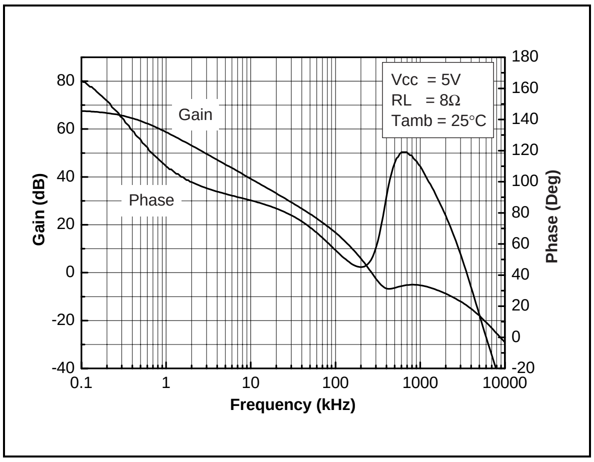


Fig. 2: Open Loop Gain and Phase vs Frequency

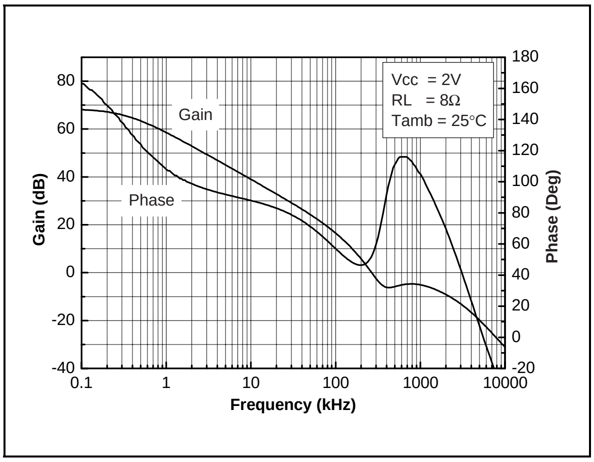


Fig. 3: Open Loop Gain and Phase vs Frequency

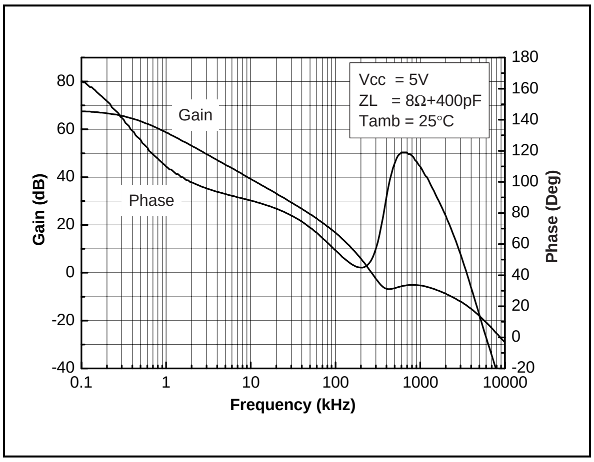


Fig. 4: Open Loop Gain and Phase vs Frequency

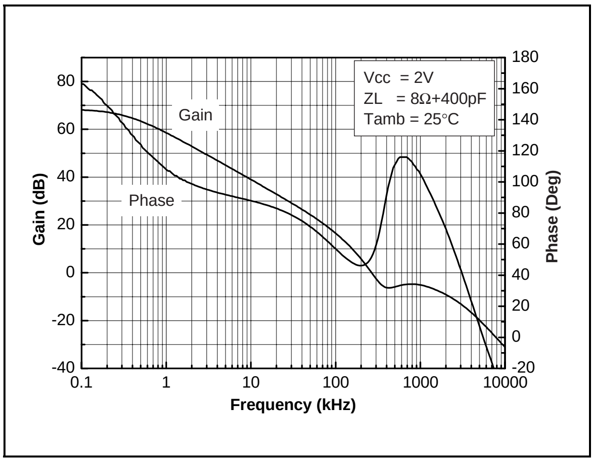


Fig. 5: Open Loop Gain and Phase vs Frequency

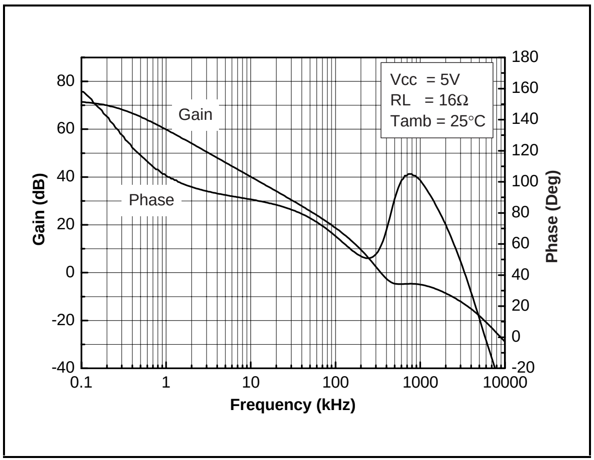


Fig. 6: Open Loop Gain and Phase vs Frequency

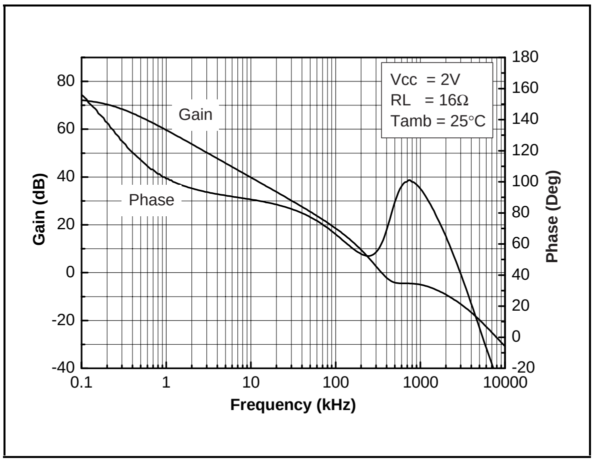


Fig. 7: Open Loop Gain and Phase vs Frequency

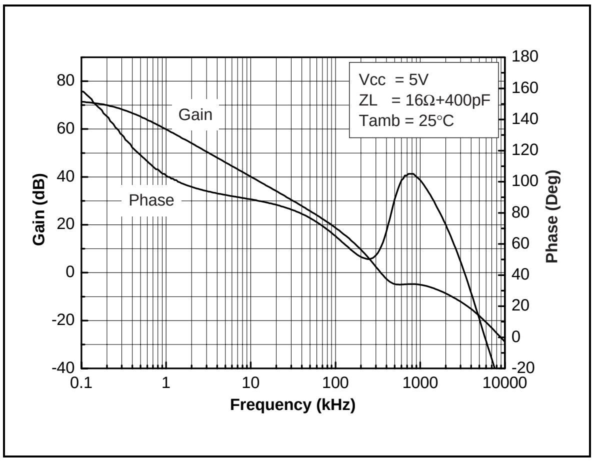


Fig. 8: Open Loop Gain and Phase vs Frequency

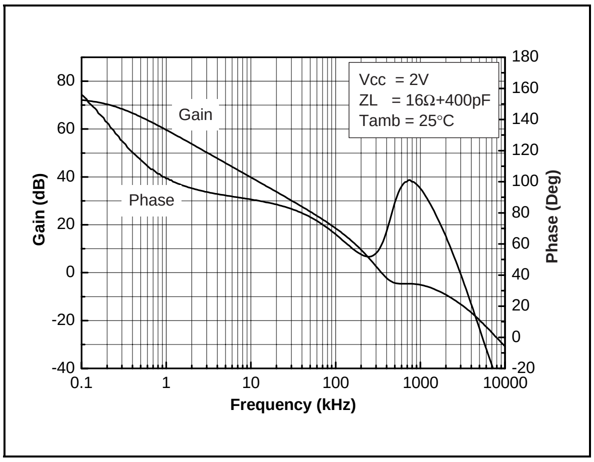


Fig. 9: Open Loop Gain and Phase vs Frequency

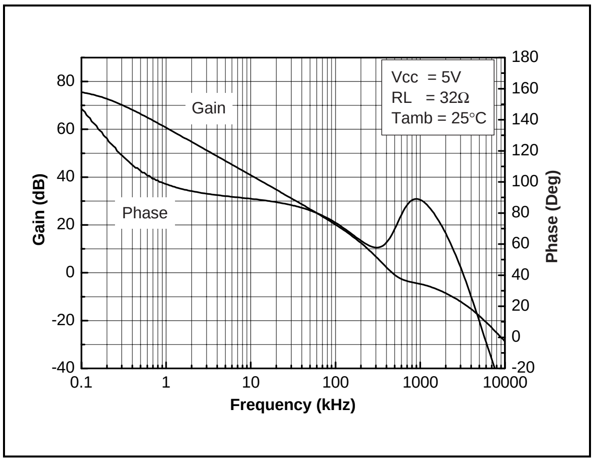


Fig. 10: Open Loop Gain and Phase vs Frequency

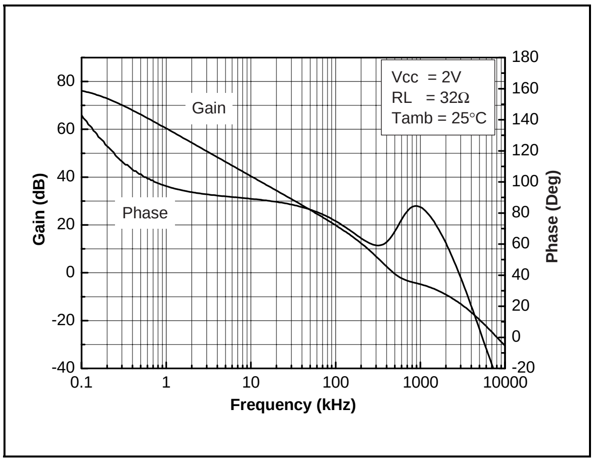


Fig. 11: Open Loop Gain and Phase vs Frequency

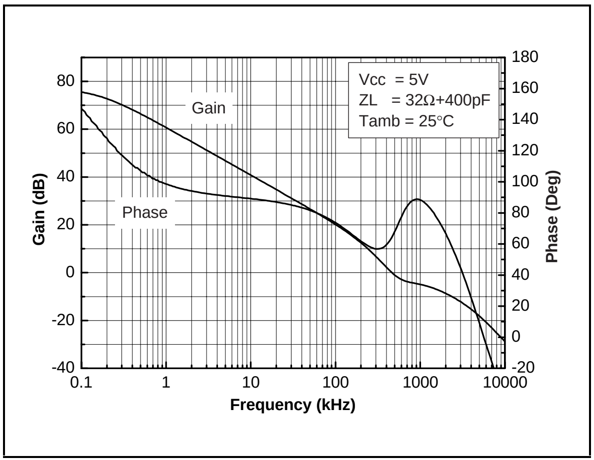


Fig. 12: Open Loop Gain and Phase vs Frequency

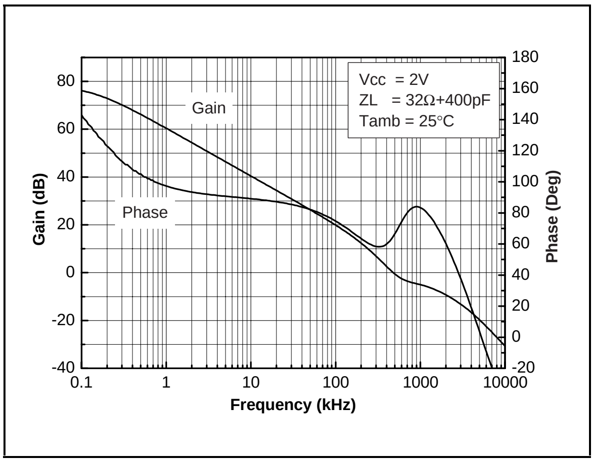


Fig. 13: Current Consumption vs Power Supply Voltage

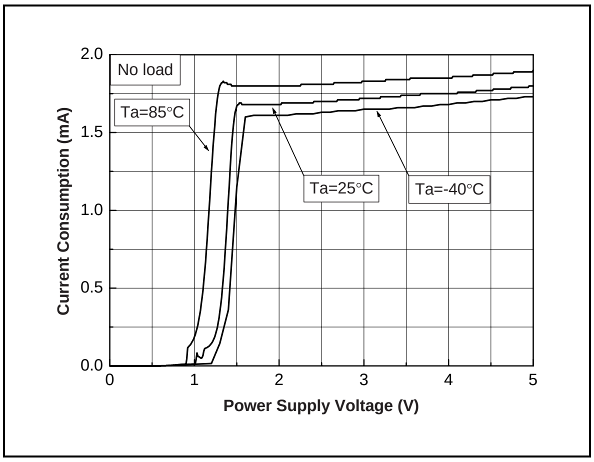


Fig. 14: Current Consumption vs Standby Voltage

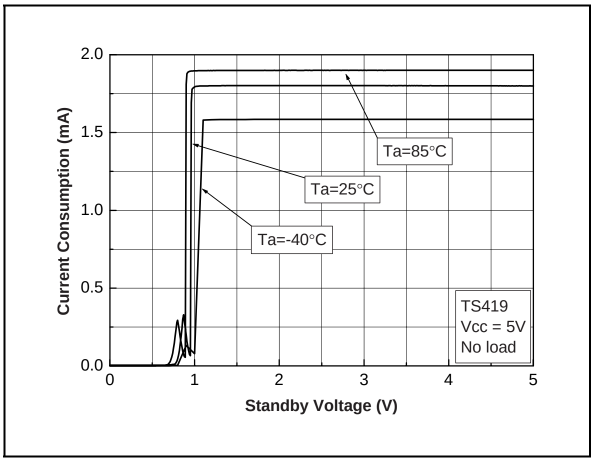


Fig. 15: Current Consumption vs Standby Voltage

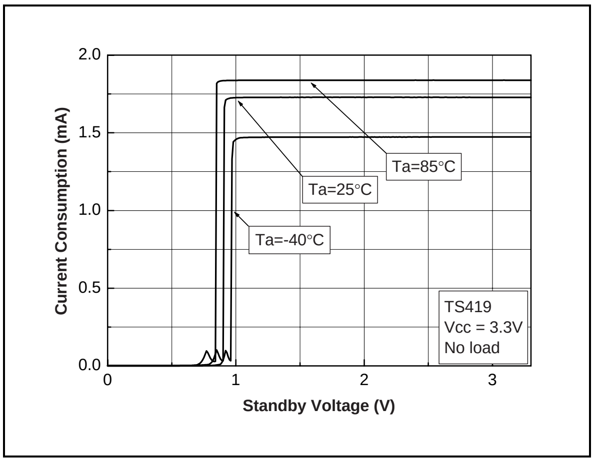


Fig. 16: Current Consumption vs Standby Voltage

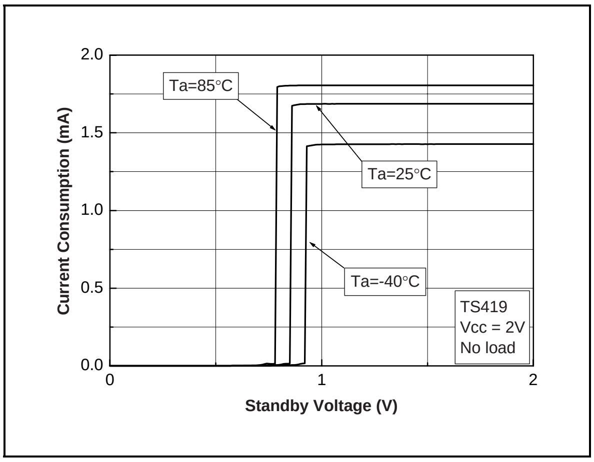


Fig. 17: Current Consumption vs Standby Voltage

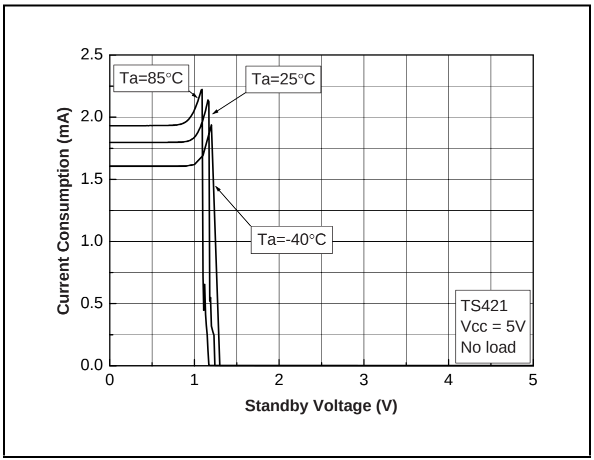


Fig. 18: Current Consumption vs Standby Voltage

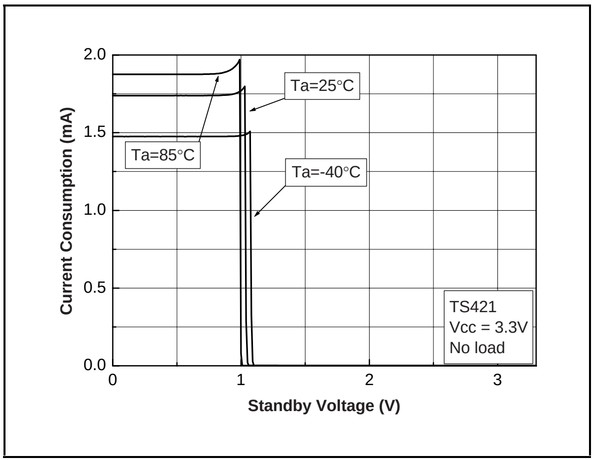


Fig. 19: Current Consumption vs Standby Voltage

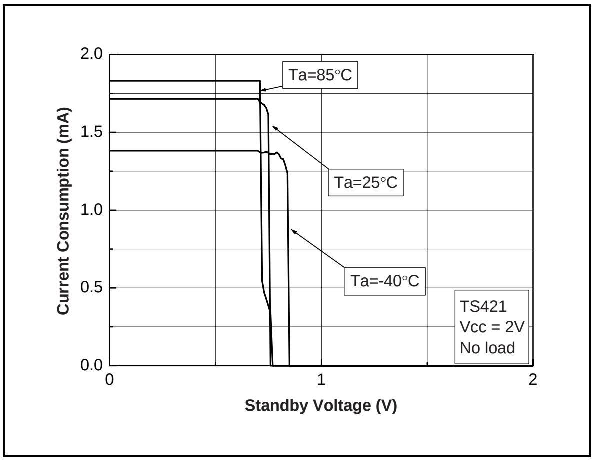


Fig. 20: Output Power vs Power Supply Voltage

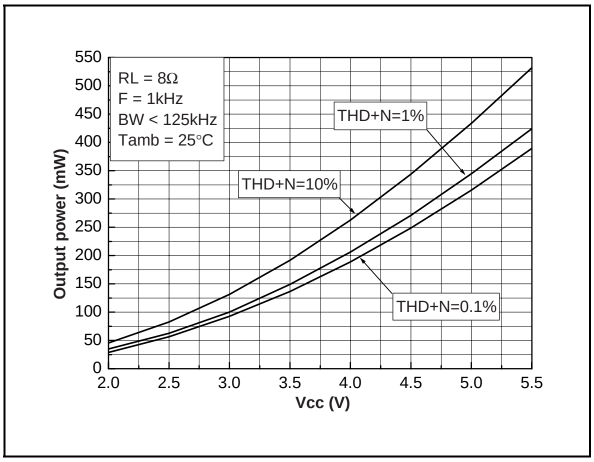


Fig. 21: Output Power vs Power Supply Voltage

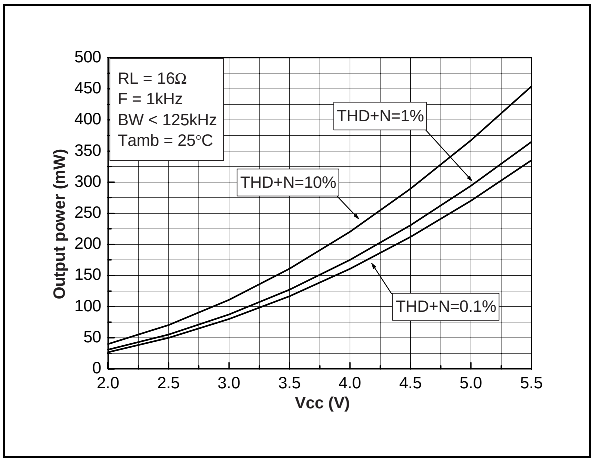


Fig. 22: Output Power vs Power Supply Voltage

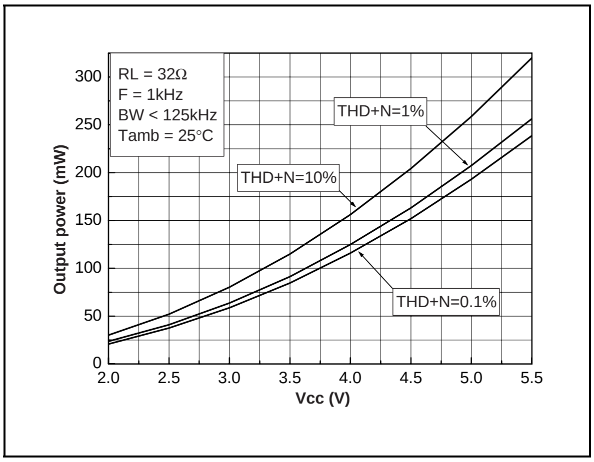


Fig. 23: Output Power vs Power Supply Voltage

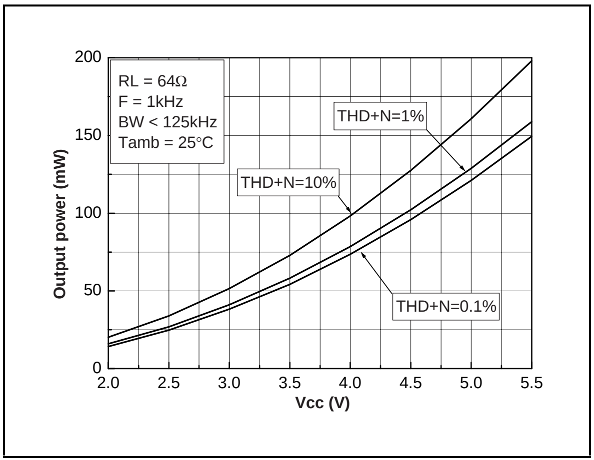


Fig. 24: Output Power vs Load Resistor

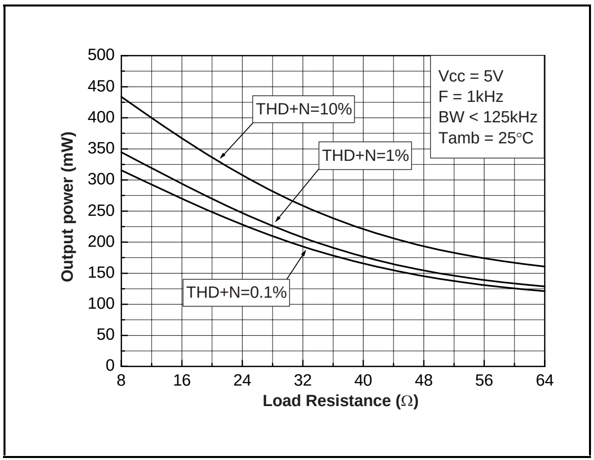


Fig. 25: Output Power vs Load Resistor

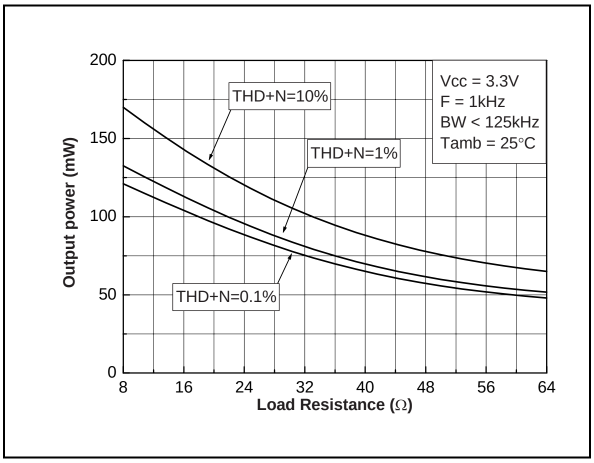


Fig. 26: Output Power vs Load Resistor

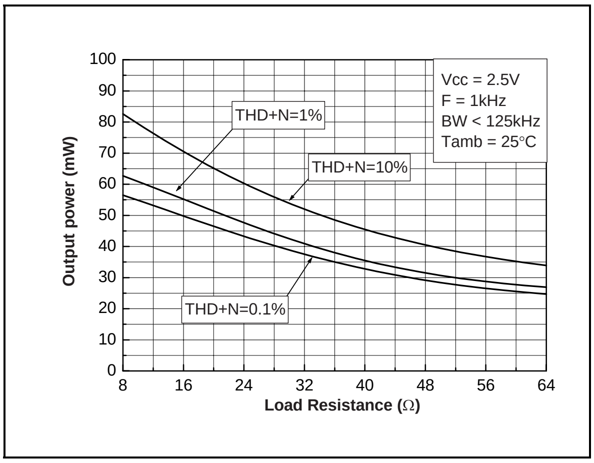


Fig. 27: Output Power vs Load Resistor

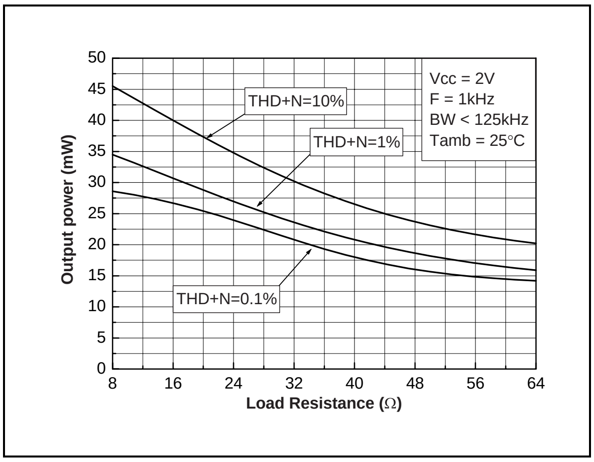


Fig. 28: Power Dissipation vs Output Power

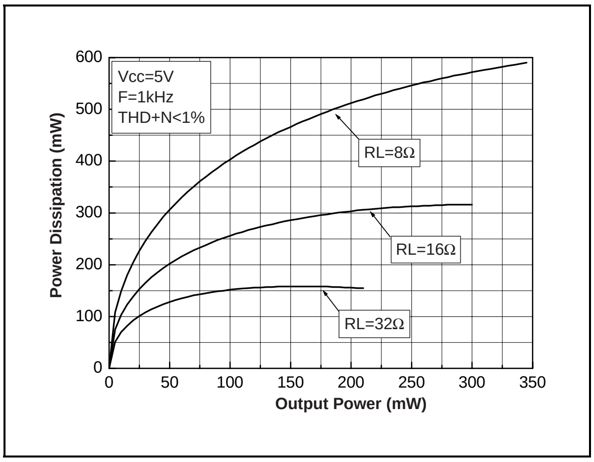


Fig. 29: Power Dissipation vs Output Power

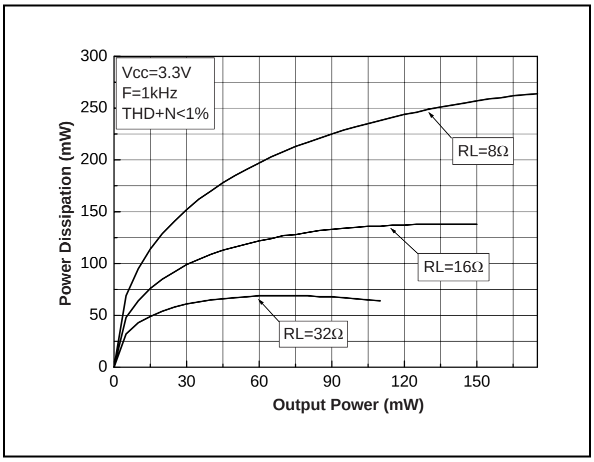


Fig. 30: Power Dissipation vs Output Power

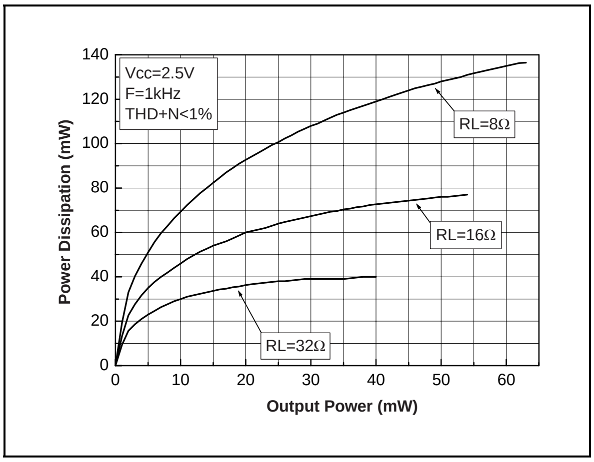


Fig. 31: Power Dissipation vs Output Power

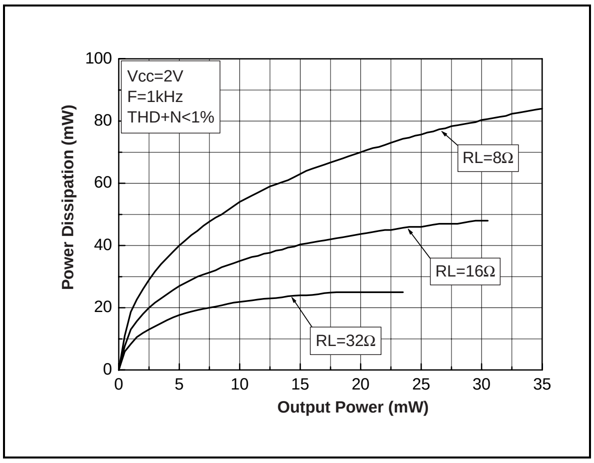


Fig. 32: Power Derating Curves

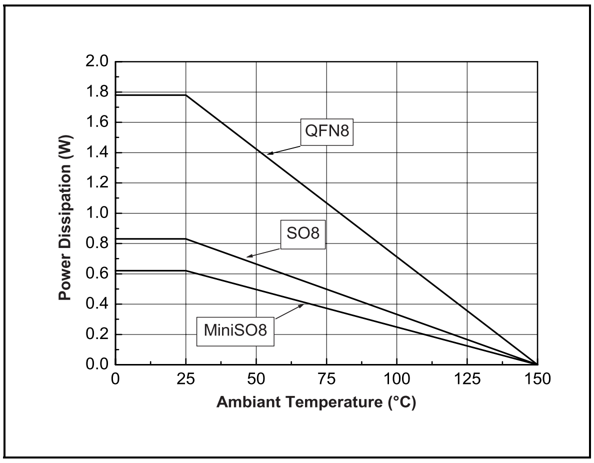


Fig. 33: Output Voltage Swing For One Amp. vs Power Supply Voltage

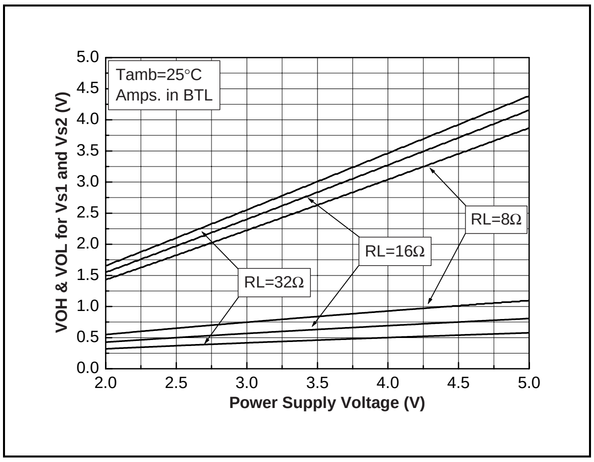


Fig. 34: Low Frequency Cut Off vs Input Capacitor for fixed gain versions

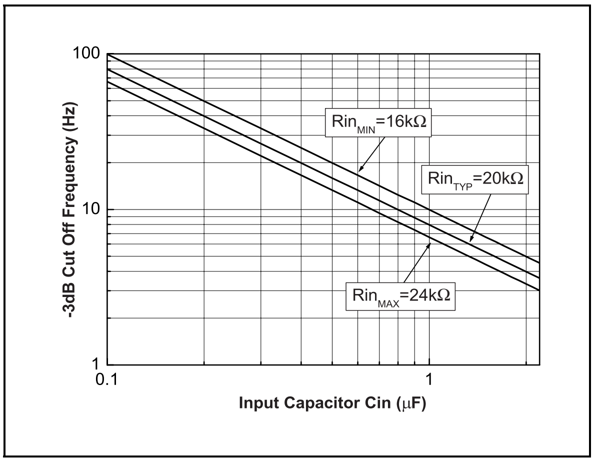


Fig. 35: THD + N vs Output Power

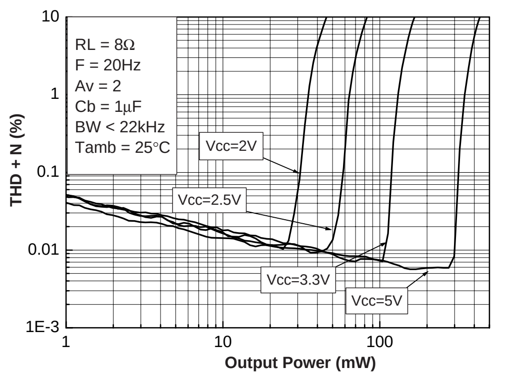


Fig. 36: THD + N vs Output Power

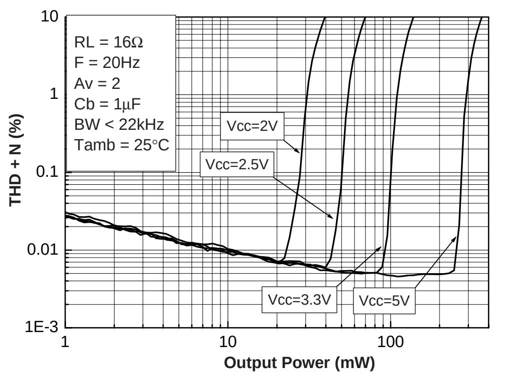


Fig. 37: THD + N vs Output Power

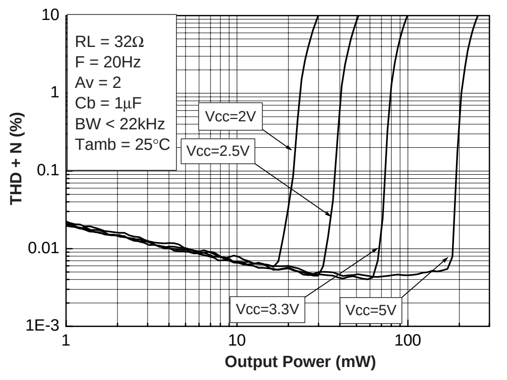


Fig. 38: THD + N vs Output Power

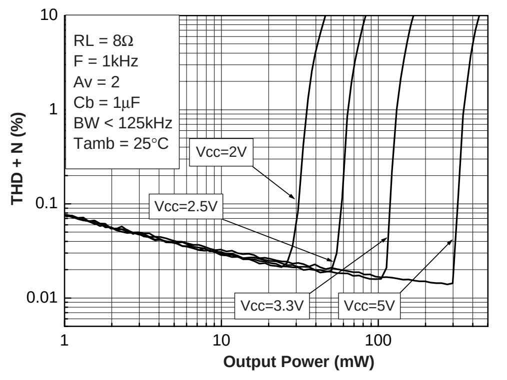


Fig. 39: THD + N vs Output Power

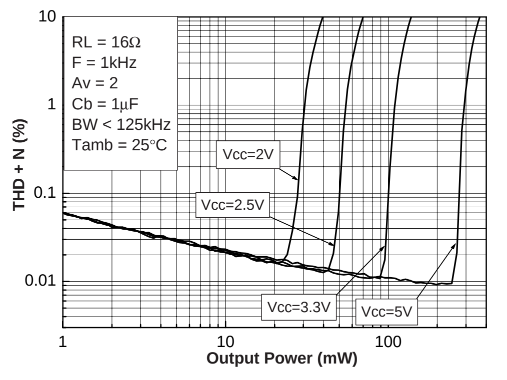


Fig. 40: THD + N vs Output Power

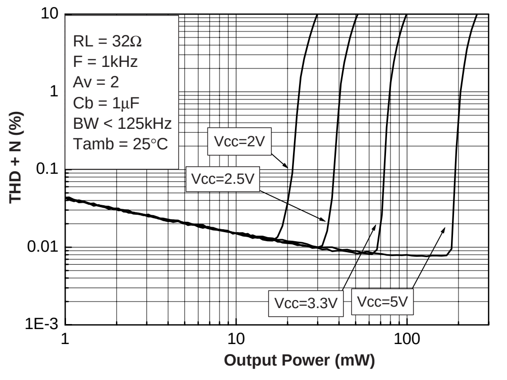


Fig. 41: THD + N vs Output Power

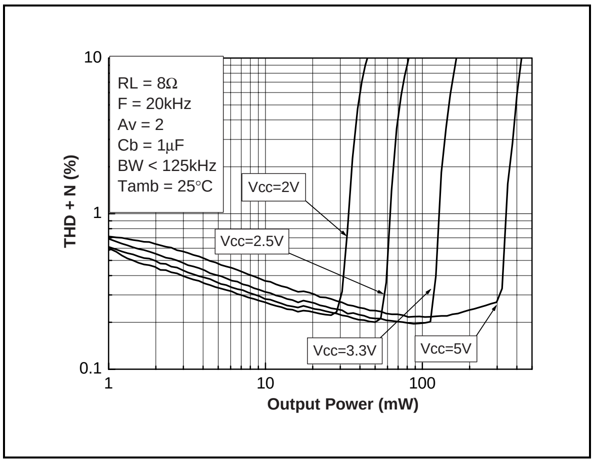


Fig. 42: THD + N vs Output Power

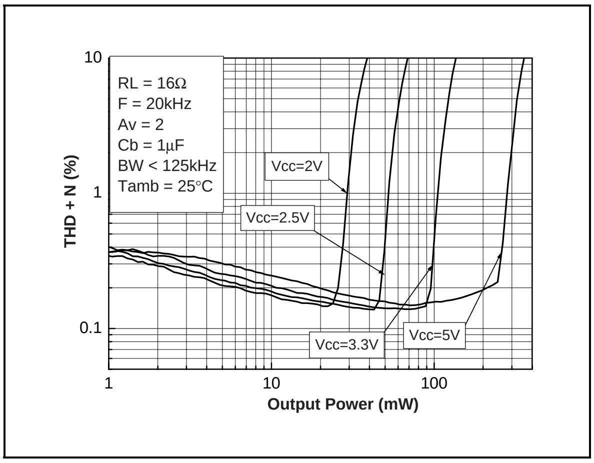


Fig. 43: THD + N vs Output Power

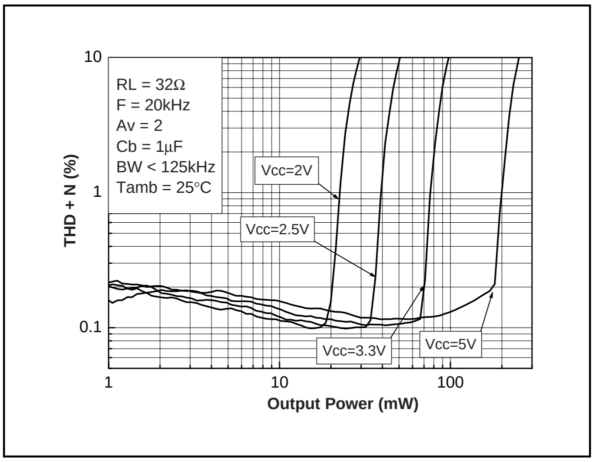


Fig. 44: THD + N vs Frequency

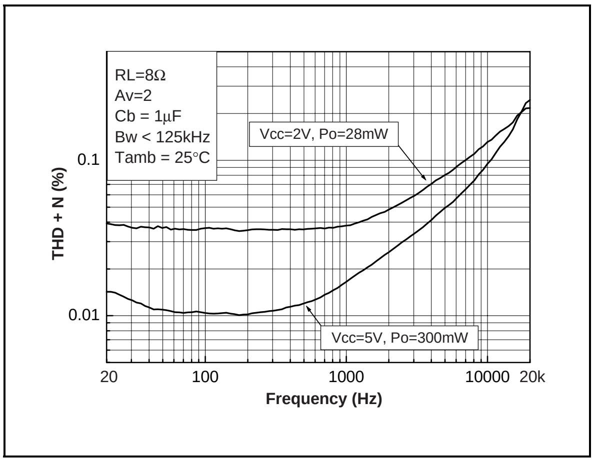


Fig. 45: THD + N vs Frequency

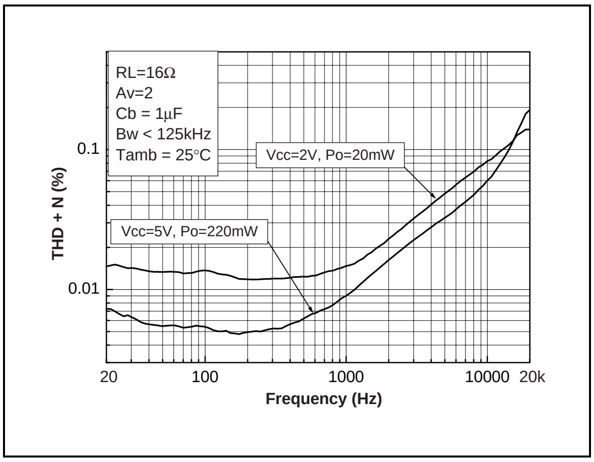


Fig. 46: THD + N vs Frequency

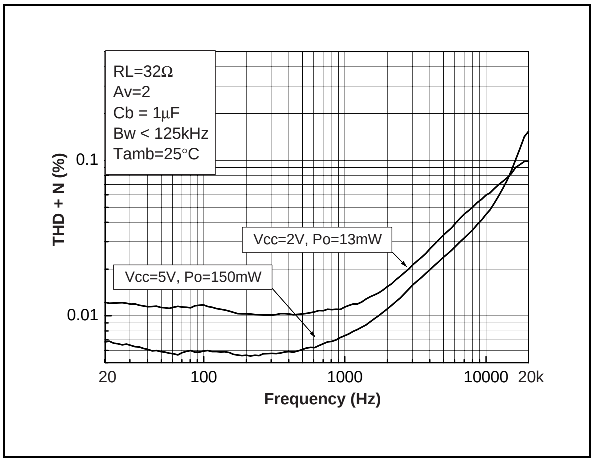


Fig. 47: Signal to Noise Ratio vs Power Supply Voltage with Unweighted Filter (20Hz to 20kHz)

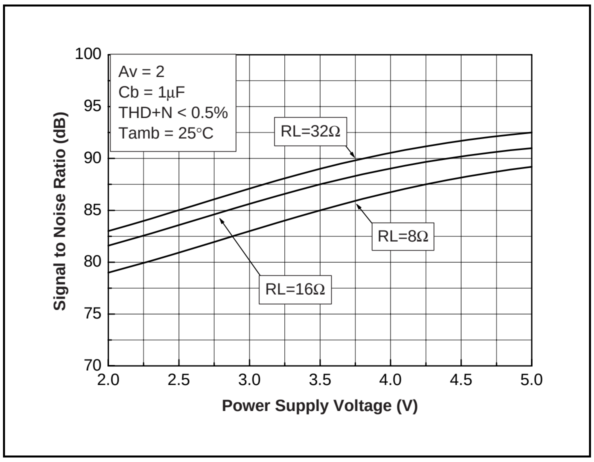


Fig. 48: Signal to Noise Ratio vs Power Supply Voltage with Weighted Filter Type A

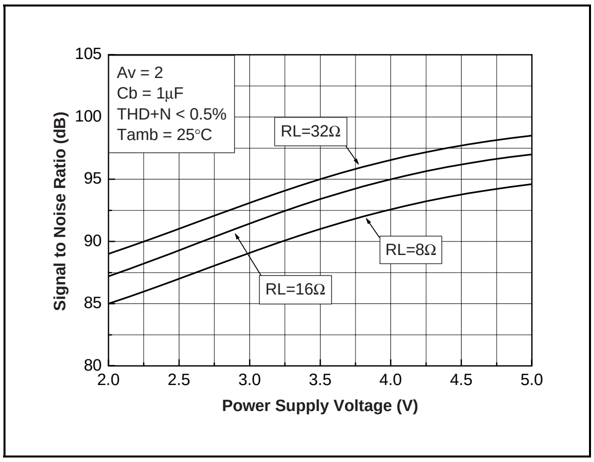


Fig. 49: Noise Floor

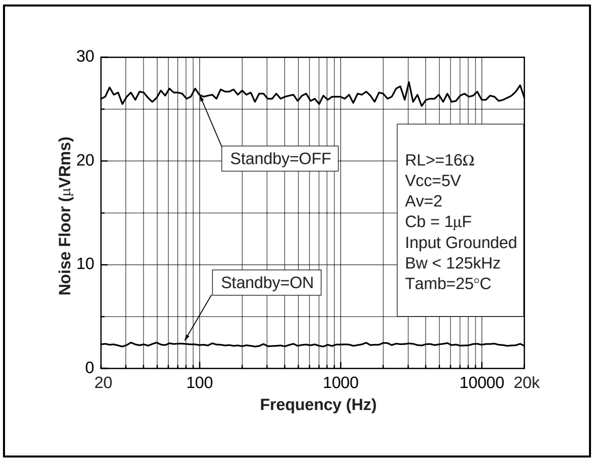


Fig. 50: Noise Floor

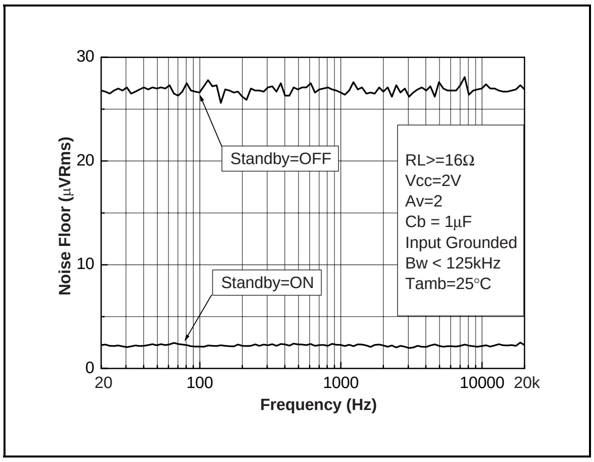


Fig. 51: PSRR vs Input Capacitor

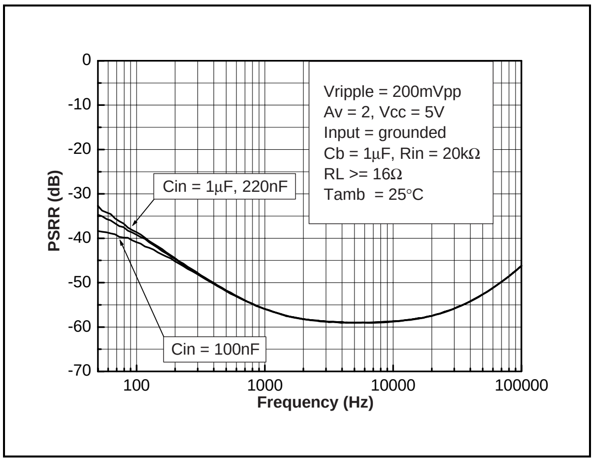


Fig. 52: PSRR vs Power Supply Voltage

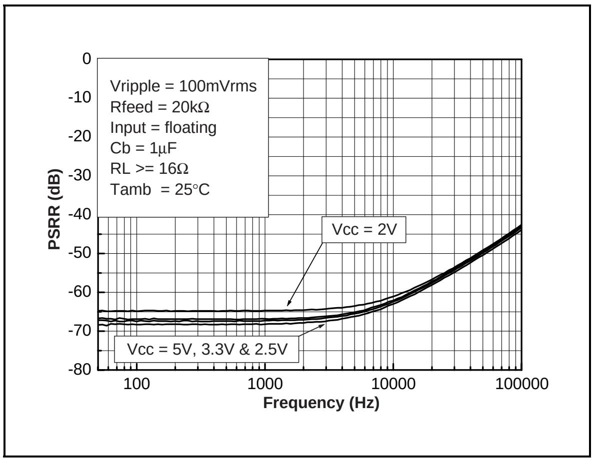


Fig. 53: PSRR vs Bypass Capacitor

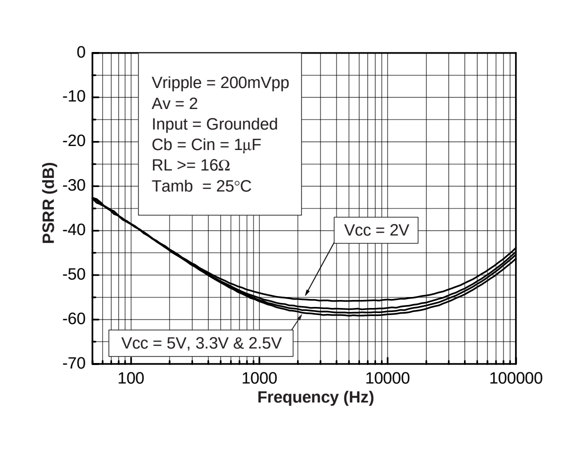


Fig. 54: PSRR vs Bypass Capacitor

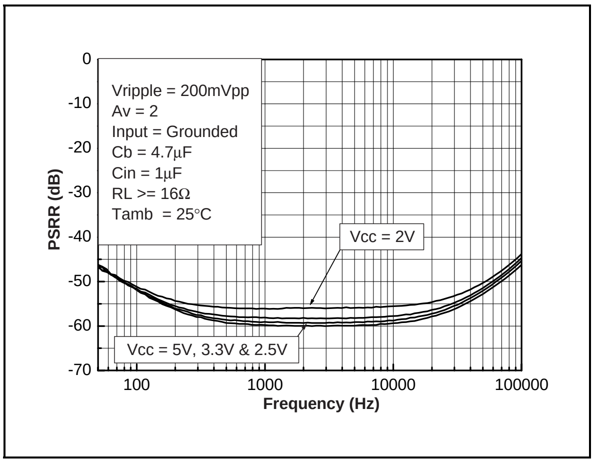


Fig. 55: PSRR vs Bypass Capacitor

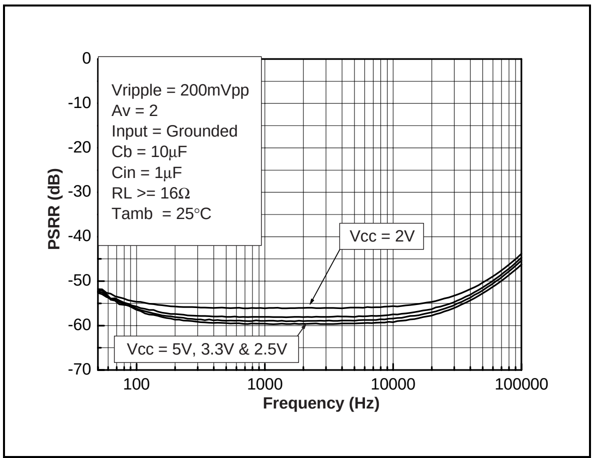


Fig. 56: THD + N vs Output Power

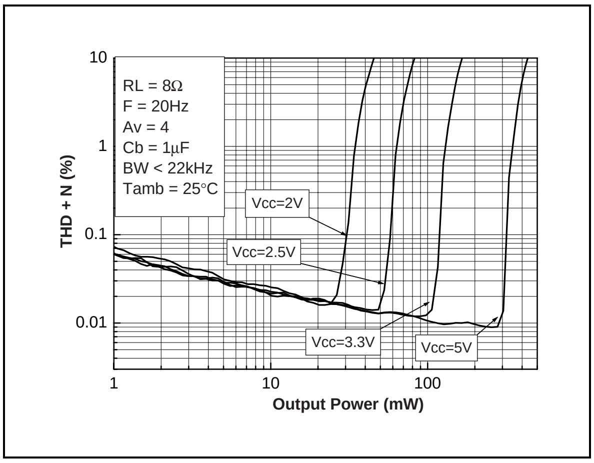


Fig. 57: THD + N vs Output Power

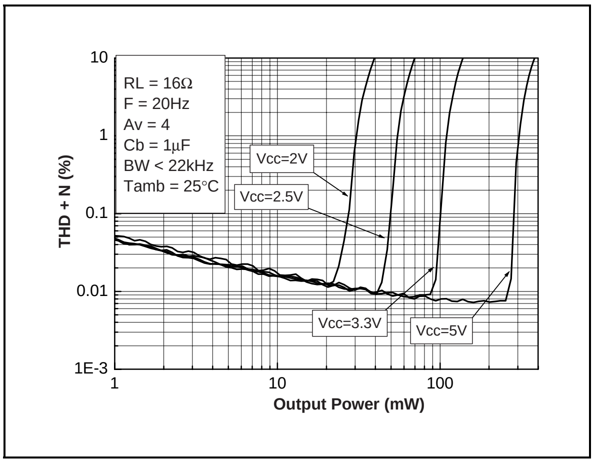


Fig. 58: THD + N vs Output Power

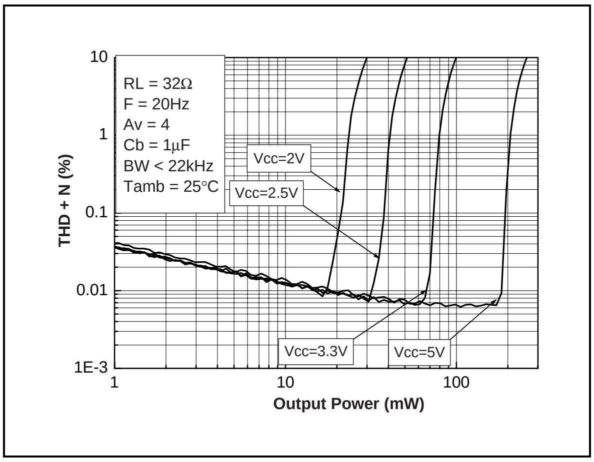


Fig. 59: THD + N vs Output Power

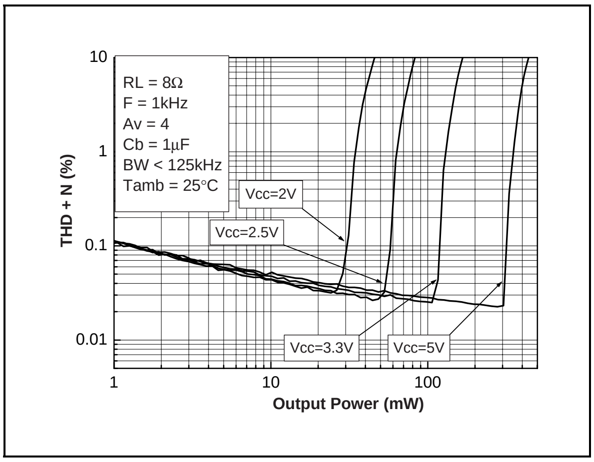


Fig. 60: THD + N vs Output Power

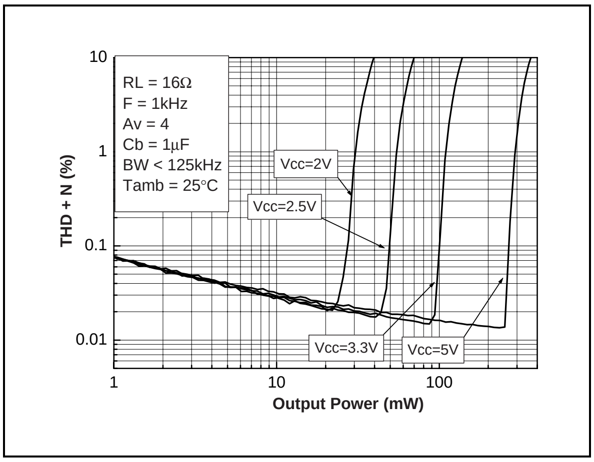


Fig. 61: THD + N vs Output Power

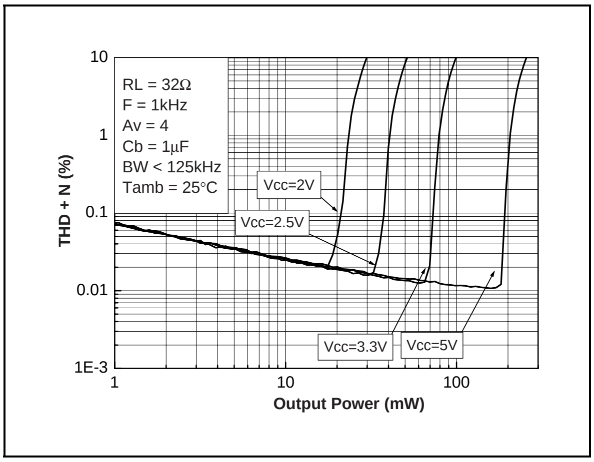


Fig. 62: THD + N vs Output Power

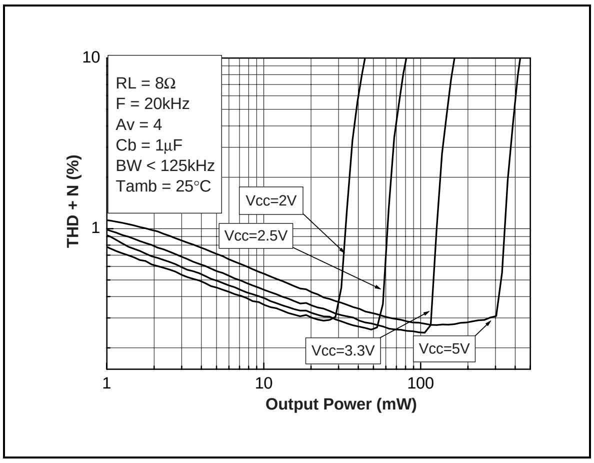


Fig. 63: THD + N vs Output Power

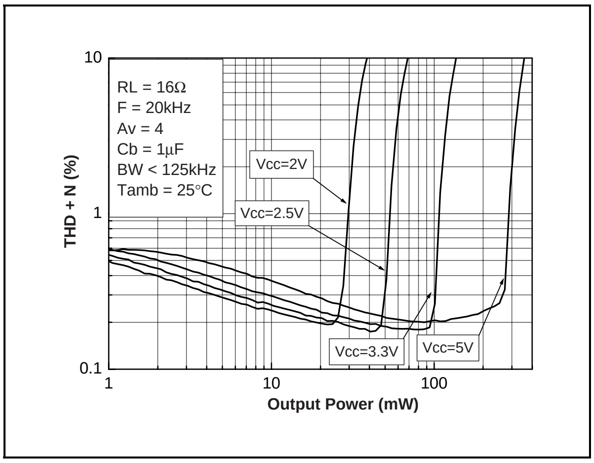


Fig. 64: THD + N vs Output Power

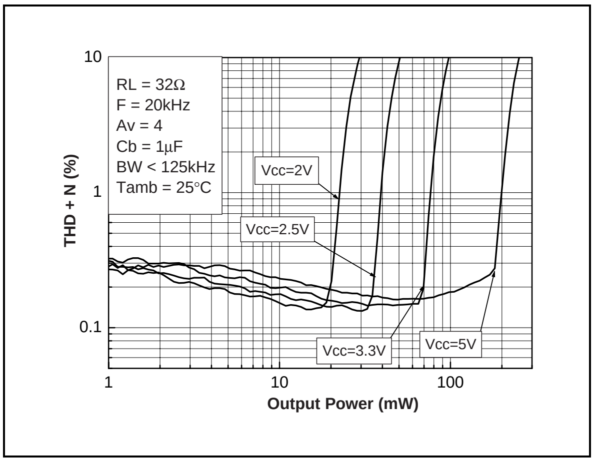


Fig. 65: THD + N vs Frequency

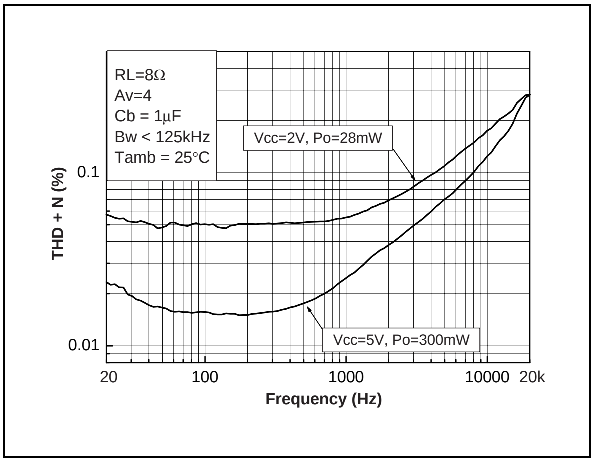


Fig. 66: THD + N vs Frequency

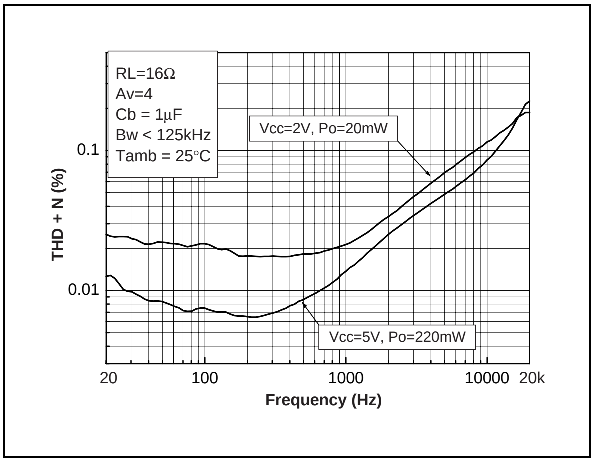


Fig. 67: THD + N vs Frequency

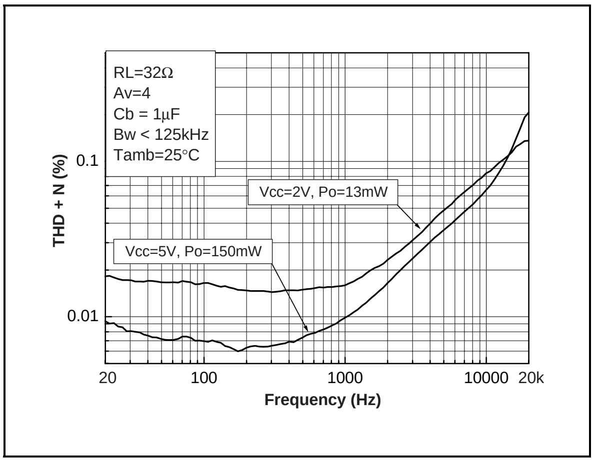


Fig. 68: Signal to Noise Ratio vs Power Supply Voltage with Unweighted Filter (20Hz to 20kHz)

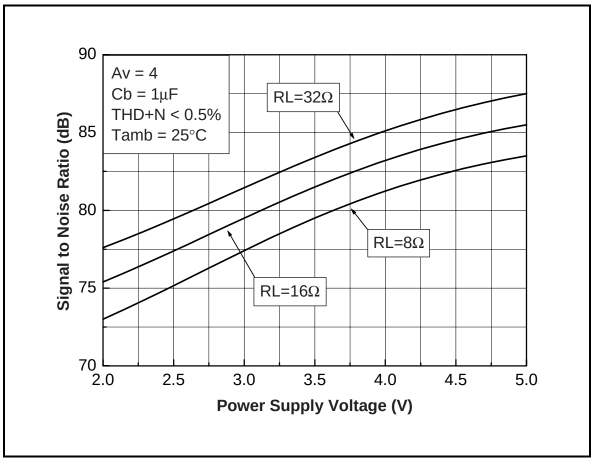


Fig. 69: Signal to Noise Ratio vs Power Supply Voltage with Weighted Filter Type A

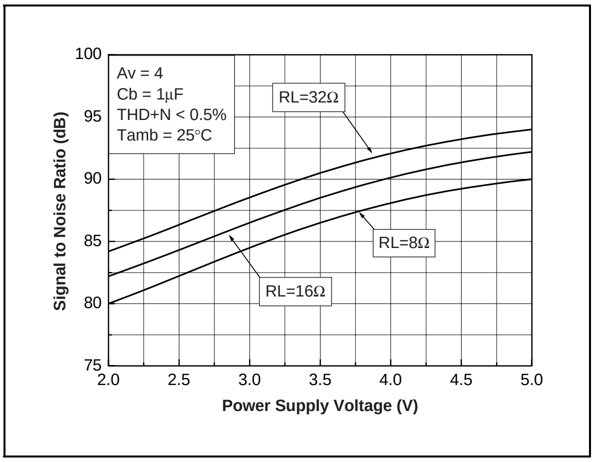


Fig. 70: Noise Floor

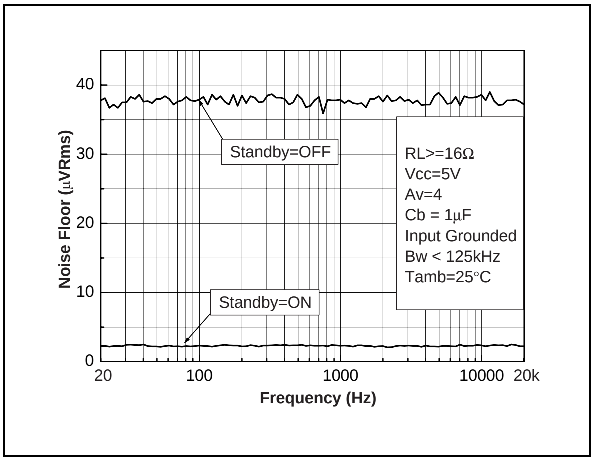


Fig. 71: Noise Floor

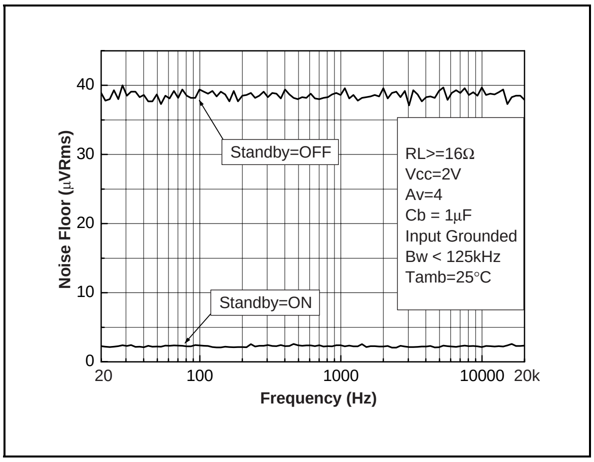


Fig. 72: PSRR vs Power Supply Voltage

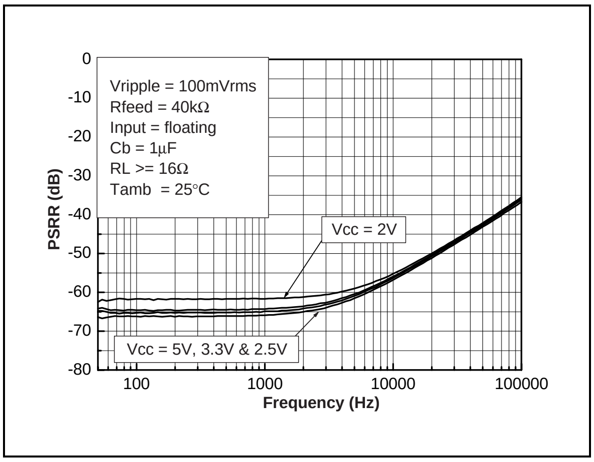


Fig. 73: PSRR vs Input Capacitor

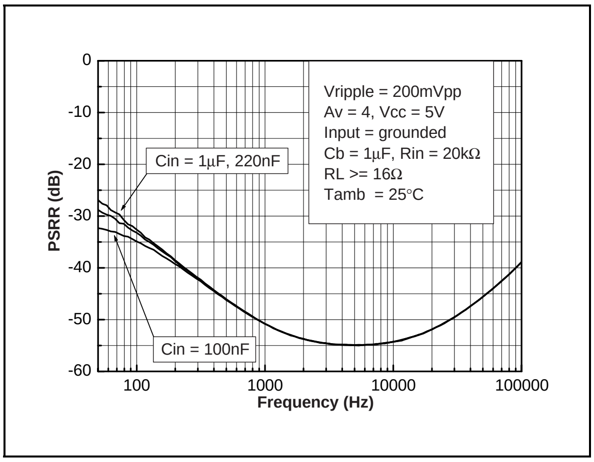


Fig. 74: PSRR vs Bypass Capacitor

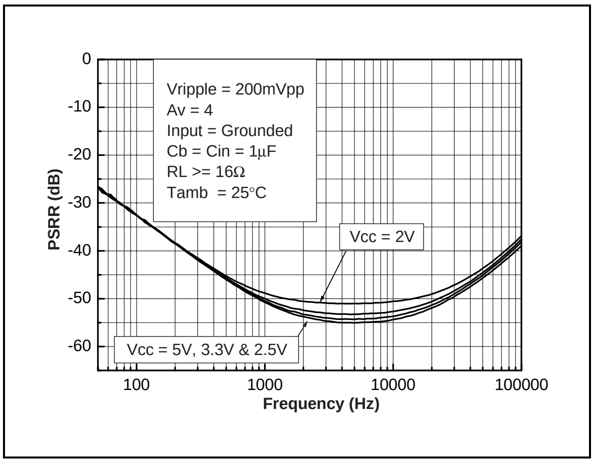


Fig. 75: PSRR vs Bypass Capacitor

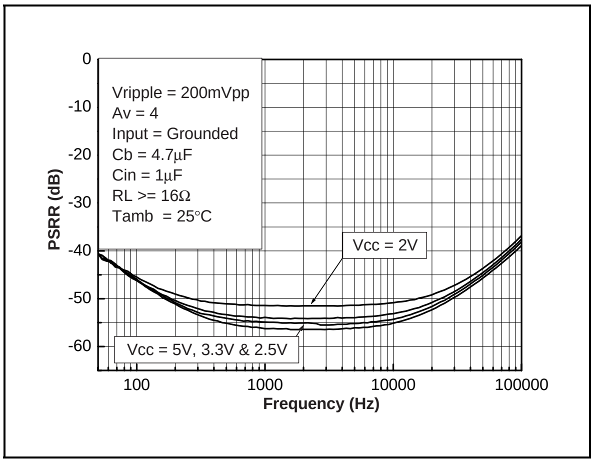


Fig. 76: PSRR vs Bypass Capacitor

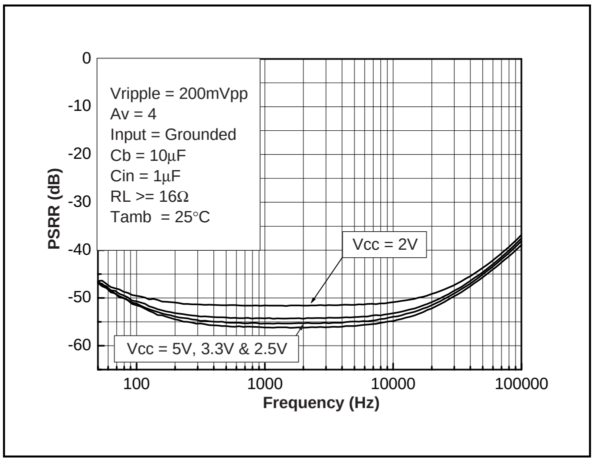


Fig. 77: THD + N vs Output Power

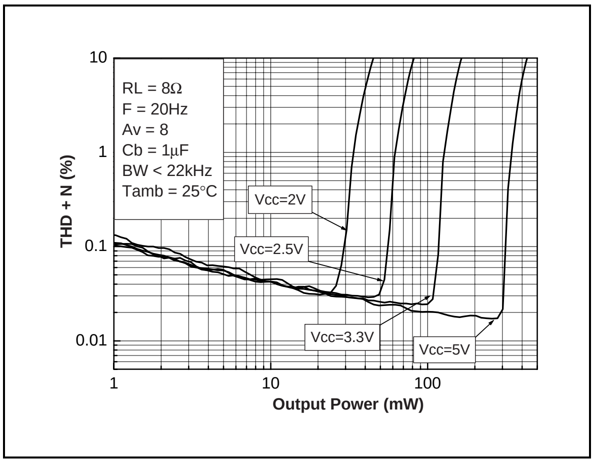


Fig. 78: THD + N vs Output Power

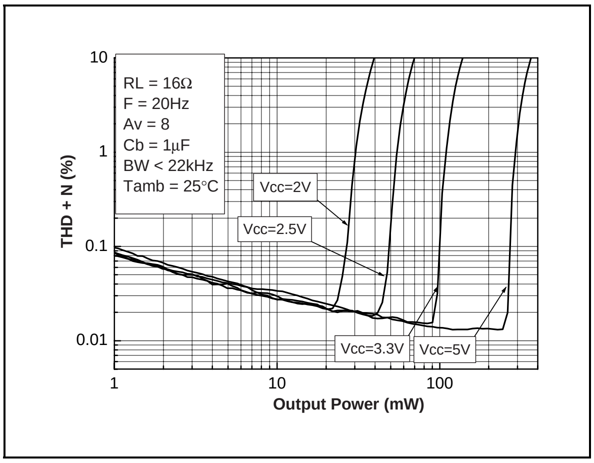


Fig. 79: THD + N vs Output Power

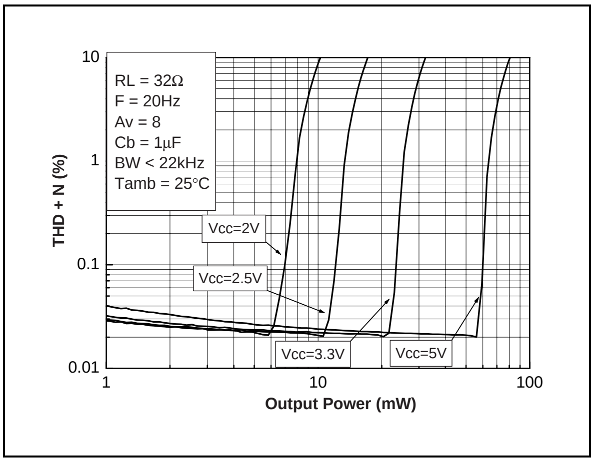


Fig. 80: THD + N vs Output Power

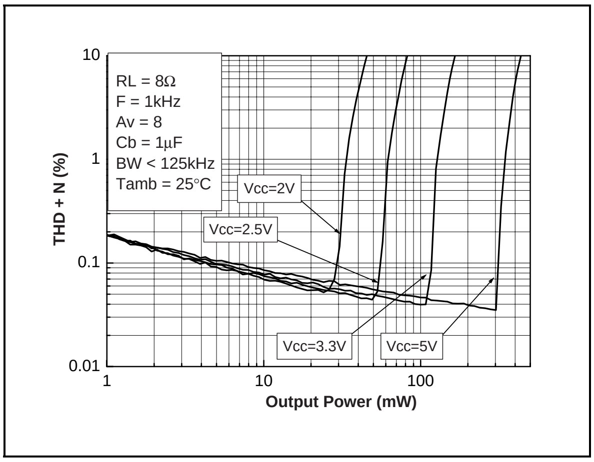


Fig. 81: THD + N vs Output Power

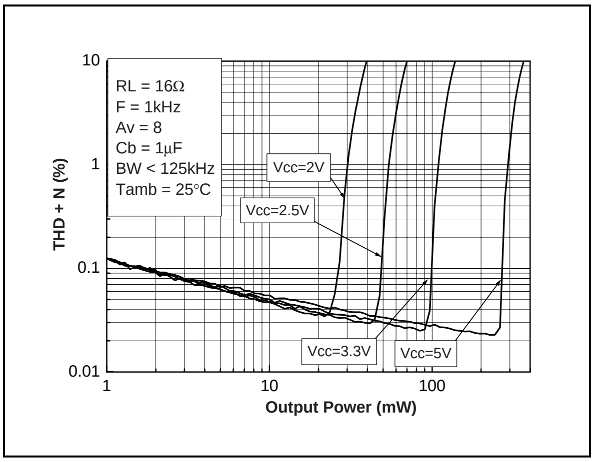


Fig. 82: THD + N vs Output Power

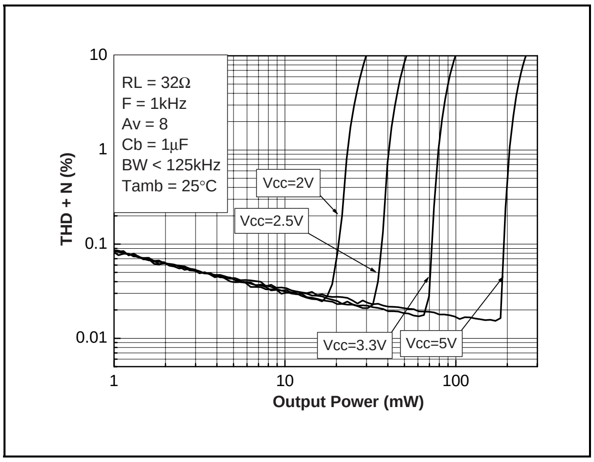


Fig. 83: THD + N vs Output Power

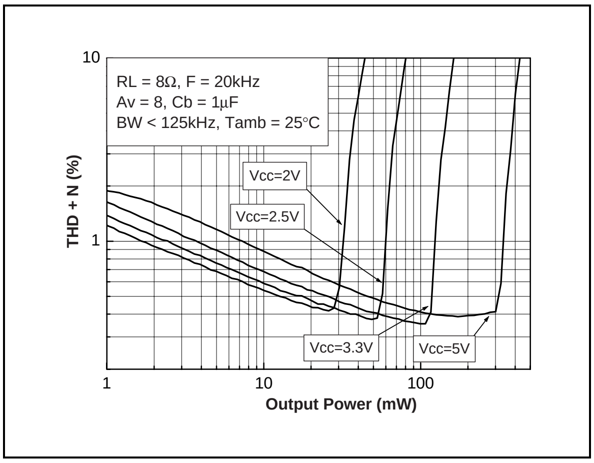


Fig. 84: THD + N vs Output Power

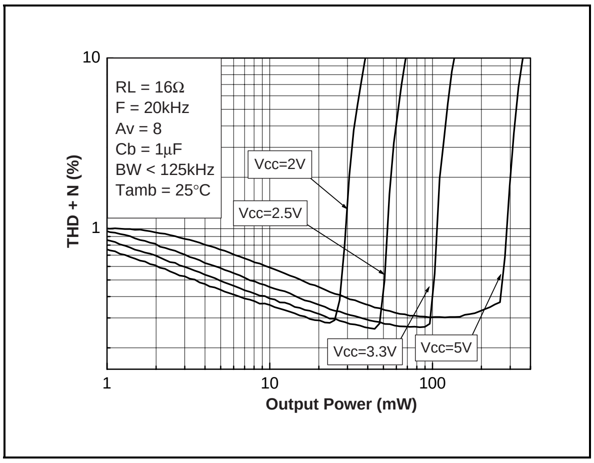


Fig. 85: THD + N vs Output Power

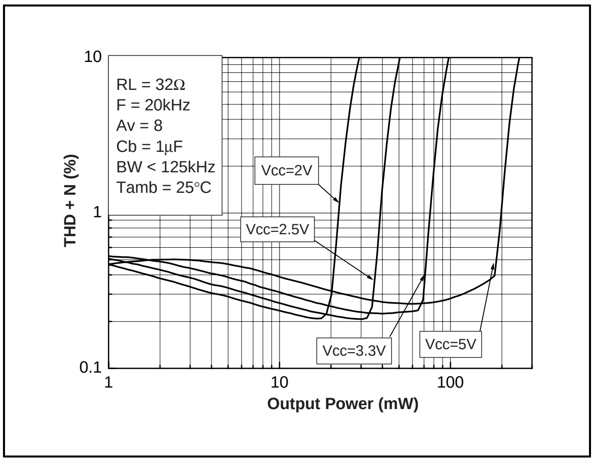


Fig. 86: THD + N vs Frequency

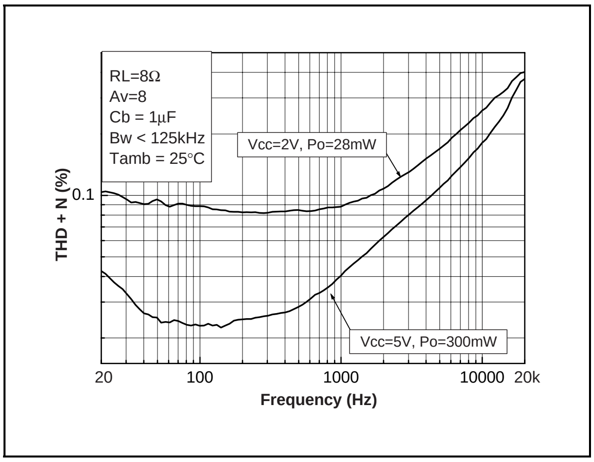


Fig. 87: THD + N vs Frequency

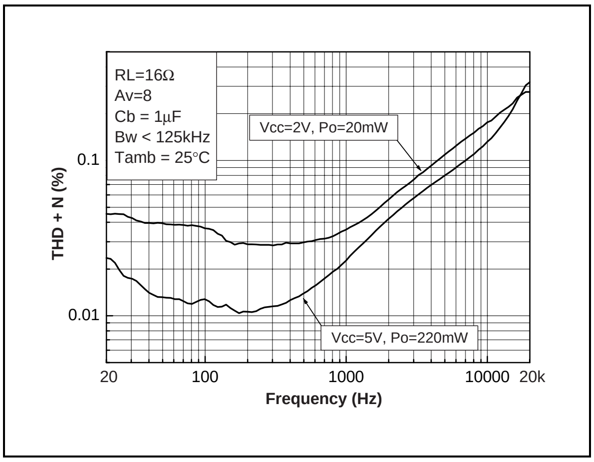


Fig. 88: THD + N vs Frequency

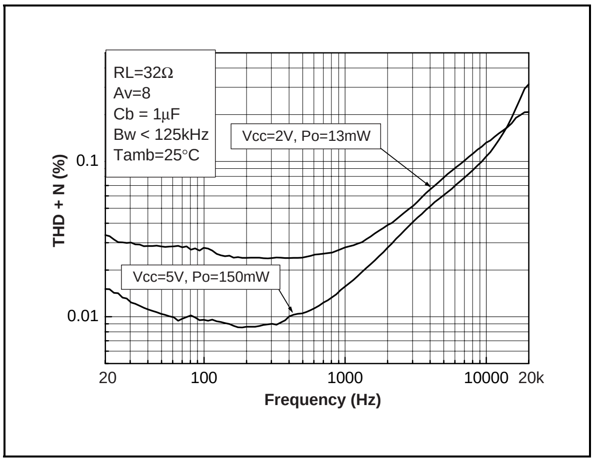


Fig. 89: Signal to Noise Ratio vs Power Supply Voltage with Unweighted Filter (20Hz to 20kHz)

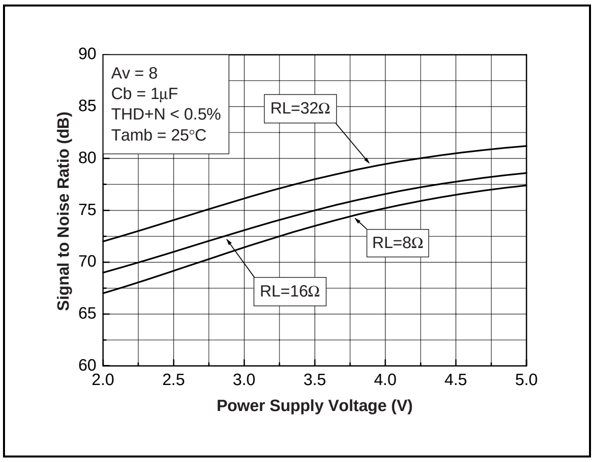


Fig. 90: Signal to Noise Ratio vs Power Supply Voltage with Weighted Filter Type A

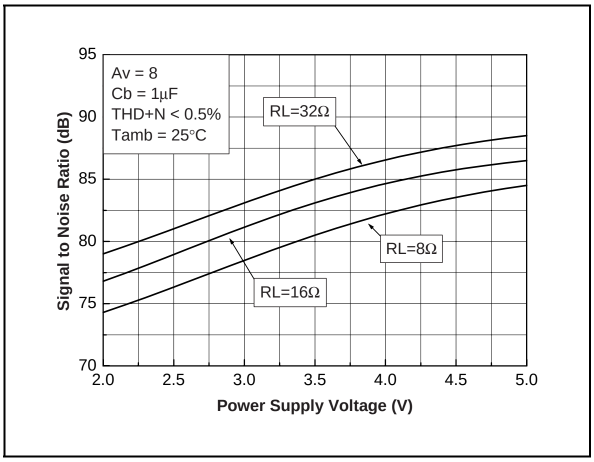


Fig. 91: Noise Floor

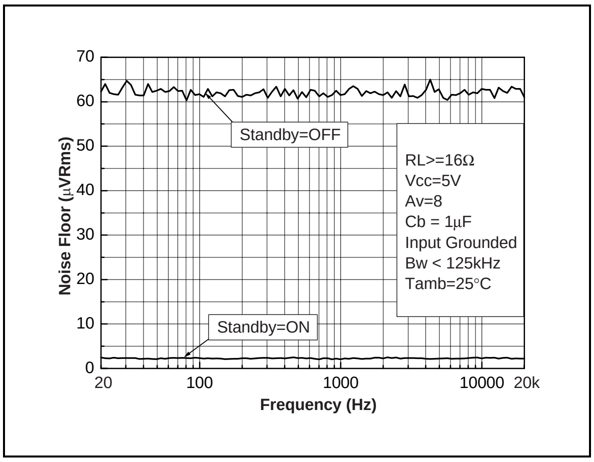


Fig. 92: Noise Floor

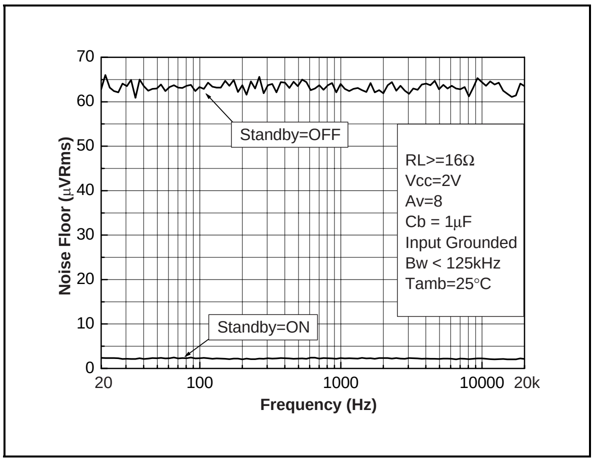


Fig. 93: PSRR vs Power Supply Voltage

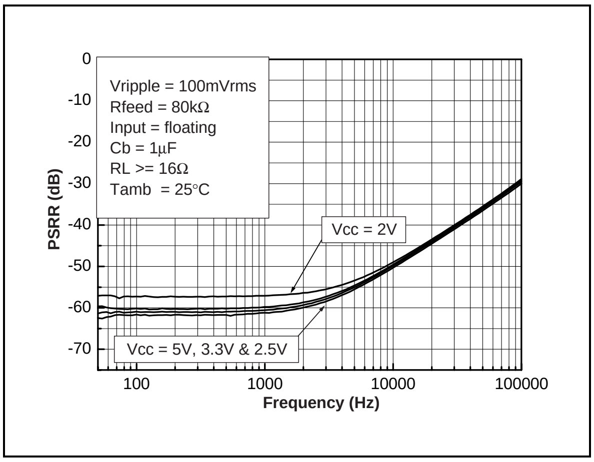


Fig. 94: PSRR vs Input Capacitor

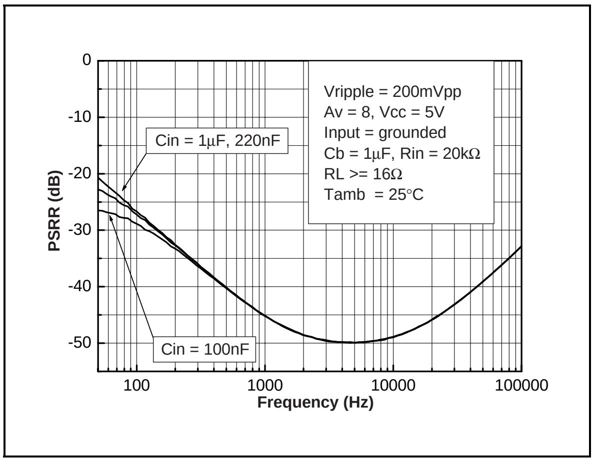


Fig. 95: PSRR vs Bypass Capacitor

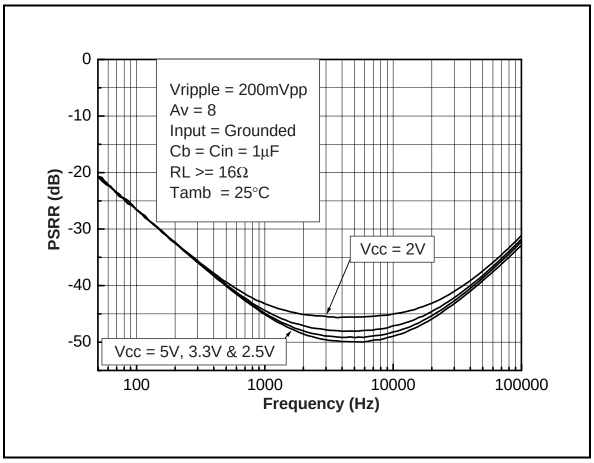


Fig. 96: PSRR vs Bypass Capacitor

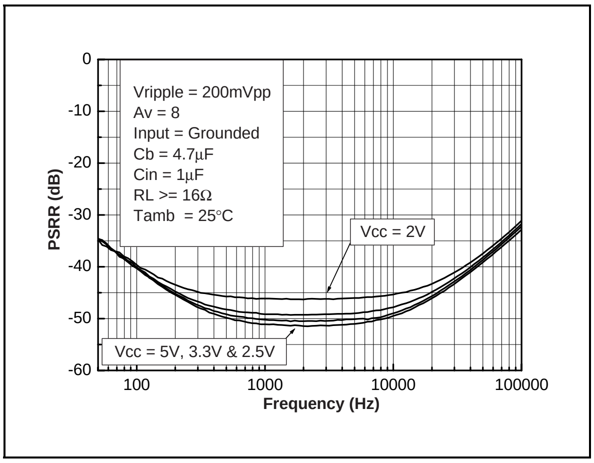
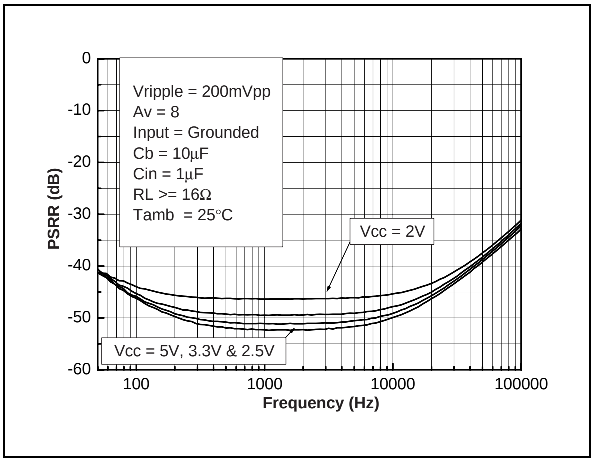


Fig. 97: PSRR vs Bypass Capacitor



APPLICATION INFORMATION

■ BTL Configuration Principle

The TS419 & TS420 are monolithic power amplifiers with a BTL output type. BTL (Bridge Tied Load) means that each end of the load is connected to two single-ended output amplifiers. Thus, we have:

Single ended output 1 = Vout1 = Vout (V)
Single ended output 2 = Vout2 = -Vout (V)

And Vout1 - Vout2 = 2Vout (V)

The output power is :

$$Pout = \frac{(2\,Vout_{RMS})^2}{R_L}\ (W)$$

For the same power supply voltage, the output power in BTL configuration is four times higher than the output power in single ended configuration.

■ Gain In Typical Application Schematic (cf. page 3 of TS419-TS421 datasheet)

In the flat region (no C_{IN} effect), the output voltage of the first stage is:

$$Vout1 = -Vin\frac{Rfeed}{Rin}\ (V)$$

For the second stage : Vout2 = -Vout1 (V)

The differential output voltage is

$$Vout2 - Vout1 = 2\,Vin\frac{Rfeed}{Rin}\ (V)$$

The differential gain named gain (Gv) for more convenient usage is :

$$Gv = \frac{Vout2 - Vout1}{Vin} = 2\frac{Rfeed}{Rin}$$

Remark : Vout2 is in phase with Vin and Vout1 is phased 180° with Vin. This means that the positive terminal of the loudspeaker should be connected to Vout2 and the negative to Vout1.

■ Low and high frequency response

In the low frequency region, C_{IN} starts to have an effect. C_{IN} forms with R_{IN} a high-pass filter with a -3dB cut off frequency .

$$F_{CL} = \frac{1}{2\pi RinCin}\ (Hz)$$

In the high frequency region, you can limit the bandwidth by adding a capacitor (Cfeed) in parallel with Rfeed. It forms a low-pass filter with a -3dB cut off frequency .

$$F_{CH} = \frac{1}{2\pi\,Rfeed\,Cfeed}\ (Hz)$$

■ Power dissipation and efficiency

Hypothesis:

- Load voltage and current are sinusoidal (Vout and Iout)
- Supply voltage is a pure DC source (Vcc)

Regarding the load we have:

$$V_{OUT} = V_{PEAK}\sin\omega t\ (V)$$

and

$$I_{OUT} = \frac{V_{OUT}}{R_L}\ (A)$$

and

$$P_{OUT} = \frac{{V_{PEAK}}^2}{2R_L}\ (W)$$

Then, the average current delivered by the supply voltage is:

$$Icc_{AVG} = 2\frac{V_{PEAK}}{\pi R_L}\ (A)$$

The power delivered by the supply voltage is:
Psupply = Vcc Icc_{AVG} (W)

Then, the **power dissipated by the amplifier** is:
Pdiss = Psupply - Pout (W)

$$Pdiss = \frac{2\sqrt{2}\,Vcc}{\pi\sqrt{R_L}}\sqrt{P_{OUT}} - P_{OUT}\ (W)$$

and the maximum value is obtained when:

$$\frac{\partial Pdiss}{\partial P_{OUT}} = 0$$

and its value is:

$$Pdiss\,max = \frac{2\,Vcc^2}{\pi^2 R_L}\ (W)$$

Remark : This maximum value is only dependent upon power supply voltage and load values.

The **efficiency** is the ratio between the output power and the power supply

$$\eta = \frac{P_{OUT}}{Psupply} = \frac{\pi V_{PEAK}}{4Vcc}$$

The maximum theoretical value is reached when Vpeak = Vcc, so

$$\frac{\pi}{4} = 78.5\%$$

■ Decoupling of the circuit

Two capacitors are needed to bypass properly the TS419/TS421. A power supply bypass capacitor C_S and a bias voltage bypass capacitor C_B.

C_S has particular influence on the THD+N in the high frequency region (above 7kHz) and an indirect influence on power supply disturbances.
With 1µF, you can expect similar THD+N performances to those shown in the datasheet.

In the high frequency region, if C_S is lower than 1µF, it increases THD+N and disturbances on the power supply rail are less filtered.
On the other hand, if C_S is higher than 1µF, those disturbances on the power supply rail are more filtered.

$\mathbf{C_B}$ has an influence on THD+N at lower frequencies, but its function is critical to the final result of PSRR (with input grounded and in the lower frequency region).

If C_B is lower than 1µF, THD+N increases at lower frequencies and PSRR worsens.
If C_B is higher than 1µF, the benefit on THD+N at lower frequencies is small, but the benefit to PSRR is substantial.

Note that C_{IN} has a non-negligible effect on PSRR at lower frequencies. The lower the value of C_{IN}, the higher the PSRR.

■ Wake-up Time: T_{WU}

When standby is released to put the device ON, the bypass capacitor C_B will not be charged immediatly. As C_B is directly linked to the bias of the amplifier, the bias will not work properly until the C_B voltage is correct. The time to reach this voltage is called wake-up time or T_{WU} and typically equal to:
T_{WU}=0.15xC_B (s) with C_B in µF.

Due to process tolerances, the range of the wake-up time is :
0.12xCb < T_{WU} < 0.18xC_B (s) with C_B in µF

Note : When the standby command is set, the time to put the device in shutdown mode is a few microseconds.

■ Pop performance

Pop performance is intimately linked with the size of the input capacitor Cin and the bias voltage bypass capacitor C_B.

The size of C_{IN} is dependent on the lower cut-off frequency and PSRR values requested. The size of C_B is dependent on THD+N and PSRR values requested at lower frequencies.

Moreover, C_B determines the speed with which the amplifier turns ON. The slower the speed is, the softer the turn ON noise is.

The charge time of C_B is directly proportional to the internal generator resistance 150kΩ..
Then, the charge time constant for C_B is
$\boldsymbol{\tau_B = 150k\Omega x C_B}$ (s)
As C_B is directly connected to the non-inverting input (pin 2 & 3) and if we want to minimize, in amplitude and duration, the output spike on Vout1 (pin 5), C_{IN} must be charged faster than C_B. The equivalent charge time constant of C_{IN} is:
$\boldsymbol{\tau_{IN} = (Rin+Rfeed) x C_{IN}}$ (s)

Thus we have the relation:
$\boldsymbol{\tau_{IN} < \tau_B}$ (s)

Proper respect of this relation allows to minimize the pop noise.

Remark : Minimizing C_{IN} and C_B benefits both the pop phenomena, and the cost and size of the application.

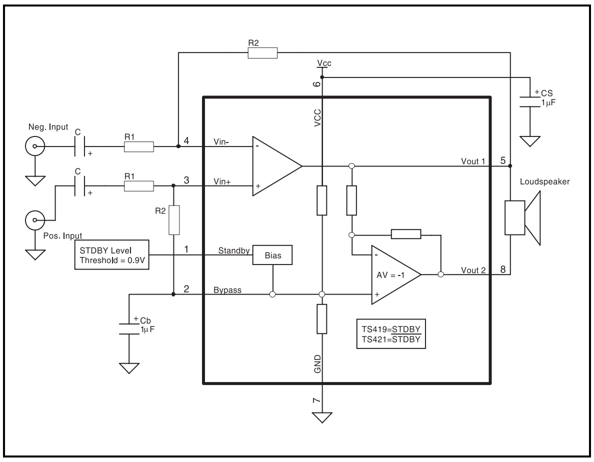
■ Application : Differential inputs BTL power amplifier.

The schematic on figure 98, shows how to design the TS419/21 to work in a differential input mode.

The gain of the amplifier is: $G_{VDIFF} = 2\frac{R_2}{R_1}$

In order to reach optimal
performances of the differential function, R_1 and R_2 should be matched at 1% max.

Fig. 98 : Differential Input Amplifier Configuration



Input capacitance C can be calculated by the following formula using the -3dB lower frequency required. (F_L is the lower frequency required)

$$C \approx \frac{1}{2\pi R_1 F_L} (F)$$

Note : This formula is true only if:

$$F_{CB} = \frac{1}{942000 \times C_B} (Hz)$$

is ten times lower than F_L.

The following bill of material is an example of a differential amplifier with a gain of 2 and a -3dB lower cuttoff frequency of about 80Hz.

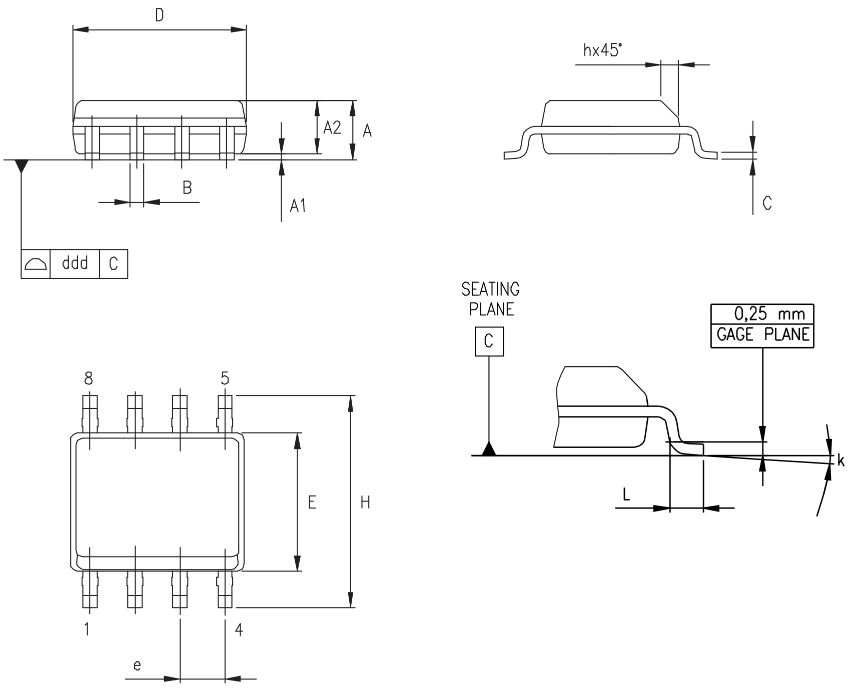
Components :

Designator	Part Type
R1	20k / 1%
R2	20k / 1%
C	100nF
C_B=C_S	1µF
U1	TS419/21

PACKAGE MECHANICAL DATA

SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	1.35		1.75	0.053		0.069
A1	0.10		0.25	0.04		0.010
A2	1.10		1.65	0.043		0.065
B	0.33		0.51	0.013		0.020
C	0.19		0.25	0.007		0.010
D	4.80		5.00	0.189		0.197
E	3.80		4.00	0.150		0.157
e		1.27			0.050	
H	5.80		6.20	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k	8° (max.)					
ddd			0.1			0.04

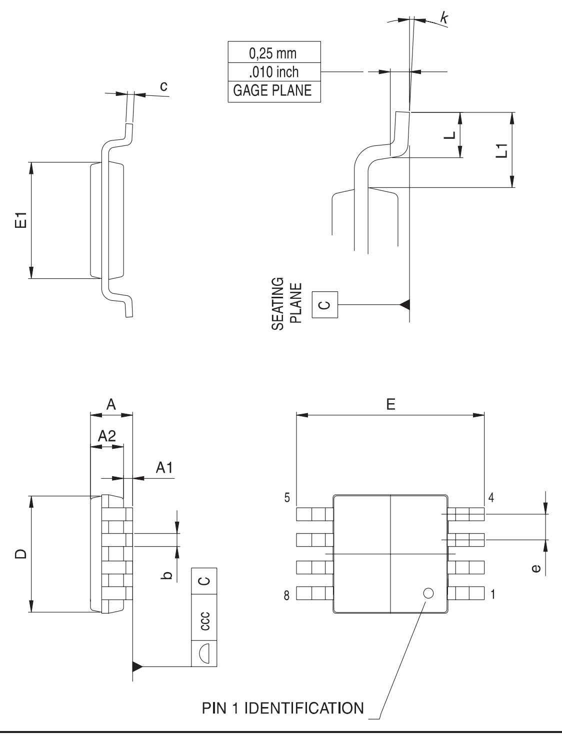


0016023/C

PACKAGE MECHANICAL DATA

miniSO-8 MECHANICAL DATA

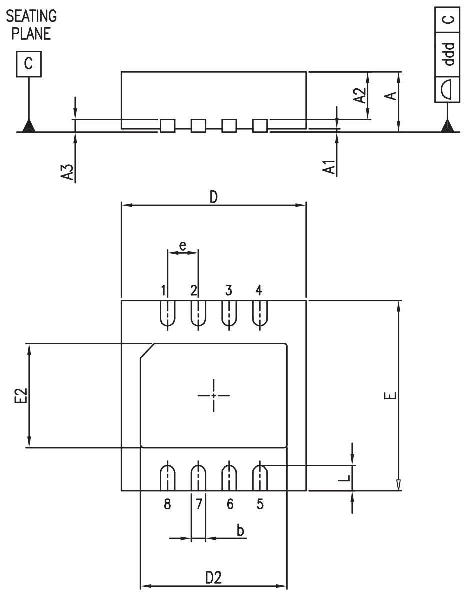
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.1			0.043
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.78	0.86	0.94	0.031	0.031	0.037
b	0.25	0.33	0.40	0.010	0.13	0.013
c	0.13	0.18	0.23	0.005	0.007	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
E	4.75	4.90	5.05	0.187	0.193	0.199
E1	2.90	3.00	3.10	.0114	0.118	0.122
e		0.65			0.026	
K	0°		6°	0°		6°
L	0.40	0.55	0.70	0.016	0.022	0.028
L1			0.10			0.004



PACKAGE MECHANICAL DATA

DFN8 (3x3) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	0.80	0.90	1.00	31.5	35.4	39.4
A1		0.02	0.05		0.8	2.0
A2		0.70			27.6	
A3		0.20			7.9	
b	0.18	0.23	0.30	7.1	9.1	11.8
D		3.00			118.1	
D2	2.23	2.38	2.48	87.8	93.7	97.7
E		3.00			118.1	
E2	1.49	1.64	1.74	58.7	64.6	68.5
e		0.50			19.7	
L	0.30	0.40	0.50	11.8	15.7	19.7



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